

RA0L1 Group

Renesas Microcontrollers

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Ultra low power 32 MHz Arm® Cortex®-M23 core, up to 64-KB code flash memory, 16-KB SRAM, Capacitive Sensing Unit (CTSU2SLa), 12-bit A/D Converter, Serial interfaces and Safety features, operating temperature range up to Ta:125°C.

Features

- Arm Cortex-M23 Core
 - Armv8-M architecture
 - Maximum operating frequency: 32 MHz
 - Debug and Trace: DWT, FPB, CoreSight[™] MTB-M23
 CoreSight Debug Port: SW-DP

Memory

- Up to 64-KB code flash memory
- 1-KB data flash memory (1,000,000 program/erase cycles)
- 16-KB SRAM
- Flash read protection (FRP)
- 128-bit unique ID

■ Connectivity

- Serial Array Unit (SAU)
 - Simplified SPI × 5
 - Simplified IIC × 6
- UART × 2 UART (LIN-bus supported) × 1 Serial Interface UARTA (UARTA) × 2
- I²C Bus interface (IICA) × 2

- 12-bit A/D Converter (ADC12)
- Temperature Sensor (TSN)

Timers

- 16-bit Timer Array Unit (TAU) × 8
- 32-bit interval timer (TML32) × 1
 - 1 channel in 32-bit counter mode
 - 2 channels in 16-bit counter mode
 - 4 channels in 8-bit counter mode

Safety

- SRAM parity error check
- Flash area protectionADC self-diagnosis function
- Cyclic Redundancy Check (CRC)
 Independent Watchdog Timer (IWDT)
- GPIO readback level detection
- Register write protectionIllegal memory access detection

■ Security

- True Random Number Generator (TRNG)
- System and Power Management
 - Low power modes
 - Realtime Clock (RTC)
 - Event Link Controller (ELC)
 - Data Transfer Controller (DTC)

 - Low Voltage Detection (LVD) with voltage settings

Multiple Clock Sources

- Main clock oscillator (MOSC) (1 to 20 MHz)
 Sub-clock oscillator (SOSC) (32.768 kHz)
- High-speed on-chip oscillator (HOCO) (24/32 MHz)
- Middle-speed on-chip oscillator (MOCO) (4 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz) Clock trim function for HOCO/MOCO/LOCO
- Clock out support
- Human Machine Interface (HMI)
 - Capacitive Touch Sensing Unit (CTSU2SLa)
 - Controlled current drive port × 8
- Up to 44 pins for general I/O ports
 - 5-V tolerance, open drain, input pull-up
- Operating Voltage
 - VCC: 1.6 to 5.5 V

Operating Temperature and Packages

- $Ta = -40 \, ^{\circ}\text{C} \text{ to } +105 \, ^{\circ}\text{C}$
 - -48-pin LFQFP (7 mm \times 7 mm, 0.5 mm pitch)
- 48-pin LFQFP (7 mm × 7 mm, 0.5 mm pitch)
 48-pin HWQFN (7 mm × 7 mm, 0.5 mm pitch)
 32-pin LQFP (7 mm × 7 mm, 0.8 mm pitch)
 32-pin HWQFN (5 mm × 5 mm, 0.5 mm pitch)
 24-pin HWQFN (4 mm × 4 mm, 0.5 mm pitch)
 20-pin LSSOP (4.4 mm × 6.5 mm, 0.65 mm pitch)
 Ta = -40 °C to +125 °C

- 1a = -40 °C to +125 °C

 48-pin LFQFP (7 mm × 7 mm, 0.5 mm pitch)

 48-pin HWQFN (7 mm × 7 mm, 0.5 mm pitch)

 32-pin LQFP (7 mm × 7 mm, 0.8 mm pitch)

 32-pin HWQFN (5 mm × 5 mm, 0.5 mm pitch)

 24-pin HWQFN (4 mm × 4 mm, 0.5 mm pitch)

 20-pin LSSOP (4.4 mm × 6.5 mm, 0.65 mm pitch)

1. Overview

The MCU integrates multiple series of software- and pin-compatible Arm®-based 32-bit cores that share a common set of Renesas peripherals to facilitate design scalability.

The MCU in this series incorporates an energy-efficient Arm Cortex[®]-M23 32-bit core, that is particularly well suited for cost-sensitive and low-power applications, with the following features:

- Up to 64-KB code flash memory
- 16-KB SRAM
- Serial Interface (SAU, UARTA, IICA)
- General Purpose Timer (TAU, TML32)
- 12-bit A/D Converter (ADC12)
- Capacitive Touch Sensing Unit (CTSU2SLa)

1.1 Function Outline

Table 1.1 Arm core

Feature	Functional description
Arm Cortex-M23 core	Maximum operating frequency: up to 32 MHz Arm Cortex-M23 core: Revision: r1p0-00rel0 Armv8-M architecture profile Single-cycle integer multiplier 19-cycle integer divider SysTick timer: Driven by SYSTICCLK (LOCO) or ICLK

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 64-KB of code flash memory.
Data flash memory	1-KB of data flash memory.
Option-setting memory	The option-setting memory determines the state of the MCU after a reset.
SRAM	On-chip SRAM with parity bit.

Table 1.3 System (1 of 2)

Feature	Functional description
Operating modes	Operating mode: • Single-chip mode
Resets	The MCU provides 7 resets (RES pin reset, power-on reset, independent watchdog timer reset, voltage monitor 0/1 resets, SRAM parity error reset, software reset).
Low Voltage Detection (LVD)	The Low Voltage Detection (LVD) module monitors the voltage level input to the VCC pin. The detection level can be selected by register settings. The LVD module consists of two separate voltage level detectors (LVD0, LVD1). LVD0 and LVD1 measure the voltage level input to the VCC pin. LVD registers allow your application to configure detection of VCC changes at various voltage thresholds.
Clocks	 Main clock oscillator (MOSC) Sub-clock oscillator (SOSC) High-speed on-chip oscillator (HOCO) Middle-speed on-chip oscillator (MOCO) Low-speed on-chip oscillator (LOCO) Clock output / Buzzer output support
Interrupt Controller Unit (ICU)	The Interrupt Controller Unit (ICU) controls which event signals are linked to the Nested Vector Interrupt Controller (NVIC), and the Data Transfer Controller (DTC) modules. The ICU also controls non-maskable interrupts.

Table 1.3 System (2 of 2)

Feature	Functional description
Low power modes	Power consumption can be reduced in multiple ways, including setting clock dividers, stopping modules, selecting power control mode in normal operation, and transitioning to low power modes.
Register write protection	The register write protection function protects important registers from being overwritten due to software errors. The registers to be protected are set with the Protect Register (PRCR).
Flash Read Protection	The MCU incorporates the flash read protection with one secure regions that include the code flash. The secure region can be protected from non-secure program accesses. A non-secure program cannot access a protected region.
Independent Watchdog Timer (IWDT)	The Independent Watchdog Timer (IWDT) consists of a 14-bit down counter that must be serviced periodically to prevent counter underflow. The IWDT provides functionality to reset the MCU or to generate a non-maskable interrupt or an underflow interrupt. Because the timer operates with the LOCO, it is particularly useful in returning the MCU to a known state as a fail-safe mechanism when the system runs out of control. The IWDT can be triggered automatically by a reset, underflow, refresh error, or a refresh of the count value in the registers.

Table 1.4 Event link

Feature	Functional description
	The Event Link Controller (ELC) uses the event requests generated by various peripheral modules as source signals to connect them to different modules, allowing direct link between the modules without CPU intervention.

Table 1.5 Direct memory access

Feature	Functional description
` '	A Data Transfer Controller (DTC) module is provided for transferring data when activated by an interrupt request.

Table 1.6 Timers

Feature	Functional description
Timer Array Unit (TAU)	The timer array unit has eight 16-bit timers. Each 16-bit timer is called a channel and can be used as an independent timer. In addition, two or more channels can be used to create a High functional timer.
32-bit Interval Timer (TML32)	The 32-bit interval timer is made up of four 8-bit interval timers (referred to as channels 0 to 3). Each is capable of operating independently and in that case they all have the same functions. Two 8-bit interval timer channels can be connected to operate as a 16-bit interval timer. Four 8-bit interval timer channels can be connected to operate as a 32-bit interval timer.
Realtime Clock (RTC)	The Realtime Clock (RTC) has the following features. Capable of counting years, months, days of the week, dates, hours, minutes, and seconds, for up to 99 years Fixed-cycle interrupt (with period selectable from among 0.5 of a second, 1 second, 1 minute, 1 hour, 1 day, or 1 month) Alarm interrupt (alarm set by day of week, hour, and minute) Pin output function of 1 Hz

Table 1.7 Communication interfaces

Feature	Functional description
Serial Array Unit (SAU)	A Serial Array Unit (SAU) has two units. Unit 0 has four channels and Unit 1 has two channels. Each channel can achieve simplified SPI, UART or simplified IIC. Only UART2 can support LIN-bus.
I ² C Bus Interface (IICA)	The I ² C Bus Interface (IICA) has 2 channels. The IICA module conforms I ² C (Inter-Integrated Circuit) Bus Interface functions.
Serial Interface UARTA (UARTA)	The Serial Interface UARTA (UARTA) has 2 channels. UARTA performs an asynchronous communication.

Table 1.8 Analog

Feature	Functional description
12-bit A/D Converter (ADC12)	A 12-bit successive approximation A/D converter is provided. Up to 13 analog input channels are selectable. Temperature sensor output and internal reference voltage are selectable for conversion.
Temperature Sensor (TSN)	The on-chip Temperature Sensor (TSN) determines and monitors the die temperature for reliable operation of the device. The sensor outputs a voltage directly proportional to the die temperature, and the relationship between the die temperature and the output voltage is fairly linear. The output voltage is provided to the ADC12 for conversion and can be further used by the end application.

Table 1.9 Human machine interfaces

Feature	Functional description
Capacitive Touch Sensing Unit (CTSU)	The Capacitive Touch Sensing Unit (CTSU) measures the electrostatic capacitance of the touch sensor. Changes in the electrostatic capacitance are determined by software that enables the CTSU to detect whether a finger is in contact with the touch sensor. The electrode surface of the touch sensor is usually enclosed with an electrical conductor so that a finger does not come into direct contact with the electrode. See section x, Capacitive Sensing Unit (CTSU).

Table 1.10 Data processing

Feature	Functional description
Cyclic Redundancy Check (CRC) calculator	The Cyclic Redundancy Check (CRC) generates CRC codes to detect errors in the data. Two CRC-generation polynomials (CRC-CCITT, CRC-32) are available.

Table 1.11 I/O ports

Feature	Functional description
I/O ports	 I/O ports for the 48-pin LFQFP/HWQFN - I/O pins: 41 - Input pins: 3 - Pull-up resistors: 26 - N-ch open-drain outputs: 28 - 5-V tolerance: 4 I/O ports for the 32-pin LQFP/HWQFN - I/O pins: 26 - Input pins: 3 - Pull-up resistors: 16 - N-ch open-drain outputs: 15 - 5-V tolerance: 2 I/O ports for the 24-pin HWQFN - I/O pins: 20 - Input pins: 1 - Pull-up resistors: 12 - N-ch open-drain outputs: 11 - 5-V tolerance: 2 I/O ports for the 20-pin LSSOP - I/O pins: 16 - Input pins: 1 - Pull-up resistors: 12 - N-ch open-drain outputs: 9

1.2 Block Diagram

Figure 1.1 shows a block diagram of the MCU superset. Some individual devices within the group have a subset of the features.

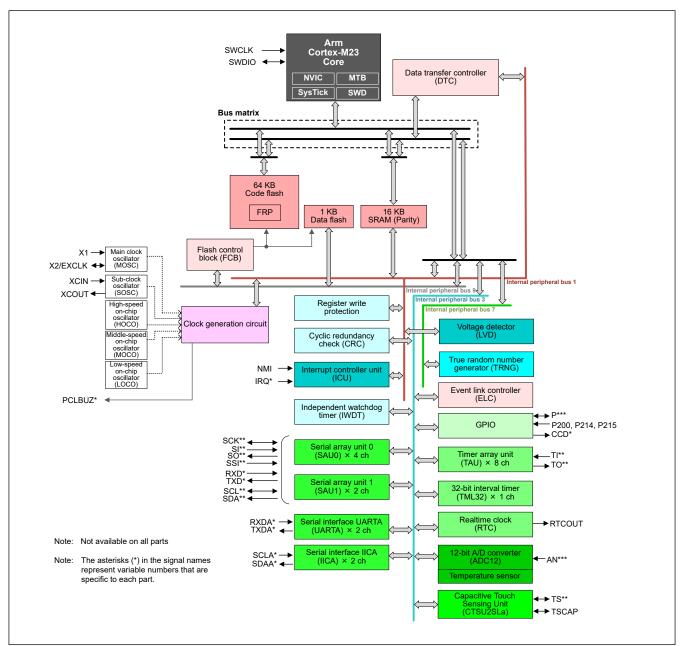


Figure 1.1 Block diagram

1.3 Part Numbering

Figure 1.2 shows the product part number information, including memory capacity and package type. Table 1.12 shows a list of products.

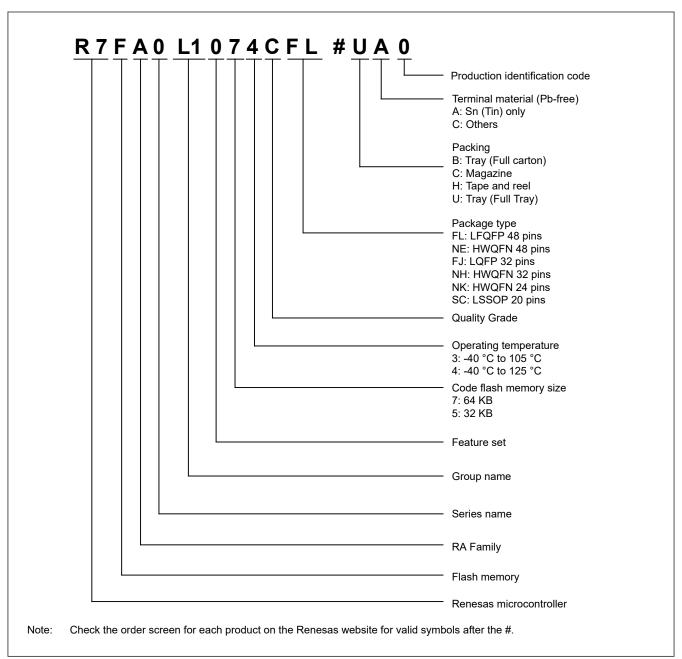


Figure 1.2 Part numbering scheme

Table 1.12 Product list

Product part number	Package code	Code flash	Data flash	SRAM	Operating temperature
R7FA0L1074CFL	PLQP0048KB-B	64 KB	1 KB	16 KB	-40 to +125 °C
R7FA0L1074CNE	PWQN0048KC-A				
R7FA0L1074CFJ	PLQP0032GB-A				
R7FA0L1074CNH	PWQN0032KE-A				
R7FA0L1074CNK	PWQN0024KG-A				
R7FA0L1074CSC	PLSP0020JB-A				
R7FA0L1073CFL	PLQP0048KB-B				-40 to +105 °C
R7FA0L1073CNE	PWQN0048KC-A				
R7FA0L1073CFJ	PLQP0032GB-A				
R7FA0L1073CNH	PWQN0032KE-A				
R7FA0L1073CNK	PWQN0024KG-A				
R7FA0L1073CSC	PLSP0020JB-A				
R7FA0L1054CFL	PLQP0048KB-B	32 KB	1 KB	16 KB	-40 to +125 °C
R7FA0L1054CNE	PWQN0048KC-A				
R7FA0L1054CFJ	PLQP0032GB-A				
R7FA0L1054CNH	PWQN0032KE-A				
R7FA0L1054CNK	PWQN0024KG-A				
R7FA0L1054CSC	PLSP0020JB-A				
R7FA0L1053CFL	PLQP0048KB-B				-40 to +105 °C
R7FA0L1053CNE	PWQN0048KC-A				
R7FA0L1053CFJ	PLQP0032GB-A				
R7FA0L1053CNH	PWQN0032KE-A				
R7FA0L1053CNK	PWQN0024KG-A				
R7FA0L1053CSC	PLSP0020JB-A				

1.4 Function Comparison

Table 1.13 Function Comparison

Parts number		R7FA0L1074CFL R7FA0L1073CFL R7FA0L1074CNE R7FA0L1073CNE	R7FA0L1054CFL R7FA0L1053CFL R7FA0L1054CNE R7FA0L1053CNE	R7FA0L1074CFJ R7FA0L1073CFJ R7FA0L1074CNH R7FA0L1073CNH	R7FA0L1054CFJ R7FA0L1053CFJ R7FA0L1054CNH R7FA0L1053CNH	R7FA0L1074CNK R7FA0L1073CNK	R7FA0L1054CNK R7FA0L1053CNK	R7FA0L1074CSC R7FA0L1073CSC	R7FA0L1054CSC R7FA0L1053CSC
Pin count		48		32		24	•	20	
Package		LFQFP/HV	/QFN	LQFP/HW0	QFN	HWQFN		LSSOP	
Code flash memory	flash memory		32 KB	64 KB	32 KB	64 KB	32 KB	64 KB	32 KB
Data flash memory		1 KB		1 KB	•	1 KB		1 KB	
SRAM (Parity)		16 KB		16 KB		16 KB		16 KB	
System	CPU clock	32 MHz		32 MHz		32 MHz		32 MHz	
	Sub-clock oscillator	Yes		Yes		Yes (CMC.	XTSEL=1)	Yes (CMC	XTSEL=1)
	ICU	Yes		Yes		Yes		Yes	
Event control	ELC	Yes		Yes		Yes		Yes	
DMA	DTC	Yes		Yes		Yes		Yes	
Timers	TAU	8 (PWM ou	itputs: 7)	8 (PWM or	itputs: 7)	8 (PWM outputs: 7)		8 (PWM outputs: 7)	
	TML32	mode), 2 (16-bit counter mode), 4 (8-		1 (32-bit counter mode), 2 (16-bit counter mode), 4 (8- bit counter mode)		1 (32-bit co mode), 2 (counter mo bit counter	16-bit ode), 4 (8-	1 (32-bit counter mode), 2 (16-bit counter mode), 4 (8- bit counter mode)	
	RTC	Yes		Yes		Yes		Yes	
	IWDT	Yes		Yes		Yes		Yes	
Communication	SAU	6 (simplified IIC), 2 (UART), 1 (UART		3 (simplified SPI), 4 (simplified IIC), 2 (UART), 1 (UART supporting LIN-bus)		3 (simplified SPI), 3 (simplified IIC), 2 (UART), 1 (UART supporting LIN-bus)		3 (simplified SPI), 3 (simplified IIC), 2 (UART), 1 (UART supporting LIN-bus)	
	UARTA	2		2		1		1	
	IICA	2		2		2		2	
Analog	ADC12	13		10		8		6	
	TSN	Yes		Yes		Yes		Yes	
НМІ	стѕи	24		14		11		9	
	CCD	8		6		6		4	
Data processing	CRC	Yes		Yes		Yes		Yes	
Security	•	TRNG		TRNG		TRNG		TRNG	
I/O ports	I/O pins	41		26		20		16	
	Input pins	3		3		1		1	
	Pull-up resistors	26		16		12		12	
	N-ch open-drain outputs	28		15		11		9	
	5-V tolerance	4		2		2		_	

1.5 Pin Functions

Table 1.14 Pin functions (1 of 2)

Function	Signal	I/O	Description
Power supply	VCC	Input	Power supply pin. Connect it to the system power supply. Connect this pin to VSS by a 0.1-µF capacitor. Place the capacitor close to the pin.
	VCL	I/O	Connect this pin to the VSS pin by the smoothing capacitor used to stabilize the internal power supply. Place the capacitor close to the pin.
	VSS	Input	Ground pin. Connect it to the system power supply (0 V).
Clock	X2	I/O	Pins for a crystal resonator. An external clock signal can be input
	X1	Input	through the X2 pin.
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal
	XCOUT	Output	resonator between XCOUT and XCIN.
	PCLBUZ0, PCLBUZ1	Output	Clock output / Buzzer output
	EXCLK	Input	External clock input for the main clock
System control	RES	Input	Reset signal input pin. The MCU enters the reset state when this signal goes low.
On-chip debug	SWDIO	I/O	Serial wire debug data input/output pin
	SWCLK	Input	Serial wire clock pin
Interrupt	NMI	Input	Non-maskable interrupt request pin
	IRQ0 to IRQ7	Input	Maskable interrupt request pins
TAU	TI00 to TI07	Input	Pins for inputting an external counting clock/capture trigger to 16-bit timers 00 to 07
	TO00 to TO07	Output	Timer output pins for 16-bit timers 00 to 07
RTC	RTCOUT	Output	Output pin for 1-Hz clock
IICA	SCLA0, SCLA1	I/O	Input/output pins for the clock
	SDAA0, SDAA1	I/O	Input/output pins for data
SAU	SCK00, SCK01, SCK10, SCK11, SCK20	I/O	Serial clock I/O pins for serial interfaces SPI00, SPI01, SPI10, SPI11, and SPI20
	SI00, SI01, SI10, SI11, SI20	Input	Serial data input pins for serial interfaces SPI00, SPI01, SPI10, SPI11, and SPI20
	SO00, SO01, SO10, SO11, SO20	Output	Serial data output pins for serial interfaces SPI00, SPI01, SPI10, SPI11, and SPI20
	SSI00	Input	Chip select pin for serial interfaces SPI00
	SCL00, SCL01, SCL10, SCL11, SCL20, SCL21	Output	Serial clock output pins for serial interfaces IIC00, IIC01, IIC10, IIC11, IIC20 and IIC21
	SDA00, SDA01, SDA10, SDA11, SDA20, SDA21	I/O	Serial data I/O pins for serial interfaces IIC00, IIC01, IIC10, IIC11, IIC20 and IIC21
	RXD0, RXD1, RXD2	Input	Serial data input pins for serial interfaces UART0, UART1, and UART2
	TXD0, TXD1, TXD2	Output	Serial data output pins for serial interfaces UART0, UART1, and UART2
UARTA	RXDA0, RXDA1	Input	Serial data input pin for the UARTA0 and UARTA1 serial interface
	TXDA0, TXDA1	Output	Serial data output pin for the UARTA0 and UARTA1 serial interface
Analog power supply	VREFH0	Input	Analog reference voltage supply pin for the ADC12. Connect this pin to external reference voltage or VCC.
	VREFL0	Input	Analog reference ground pin for the ADC12. Connect this pin to external reference ground voltage or VSS.

Table 1.14 Pin functions (2 of 2)

Function	Signal	I/O	Description
ADC12	AN000 to AN010, AN021 to AN022	Input	Input pins for the analog signals to be processed by the A/D converter.
CTSU	TS0 to TS23	I/O	Capacitive touch detection pins (touch pins)
	TSCAP	I/O	Secondary power supply pin for the touch driver
CCD	CCD0 to CCD7	Output	Controlled current drive port pins
I/O ports	P000 to P002, P008 to P015	I/O	General-purpose input/output pins
	P100 to P106, P108 to P112	I/O	General-purpose input/output pins
	P200	Input	General-purpose input pin
	P201, P206 to P208, P212, P213	I/O	General-purpose input/output pins
	P214, P215	Input	General-purpose input pins
	P300 to P302	I/O	General-purpose input/output pins
	P400, P401, P407 to P409	I/O	General-purpose input/output pins
	P500	I/O	General-purpose input/output pins
	P913 to P915	I/O	General-purpose input/output pins

1.6 Pin Assignments

Figure 1.4 to Figure 1.6 show the pin assignments from the top view.

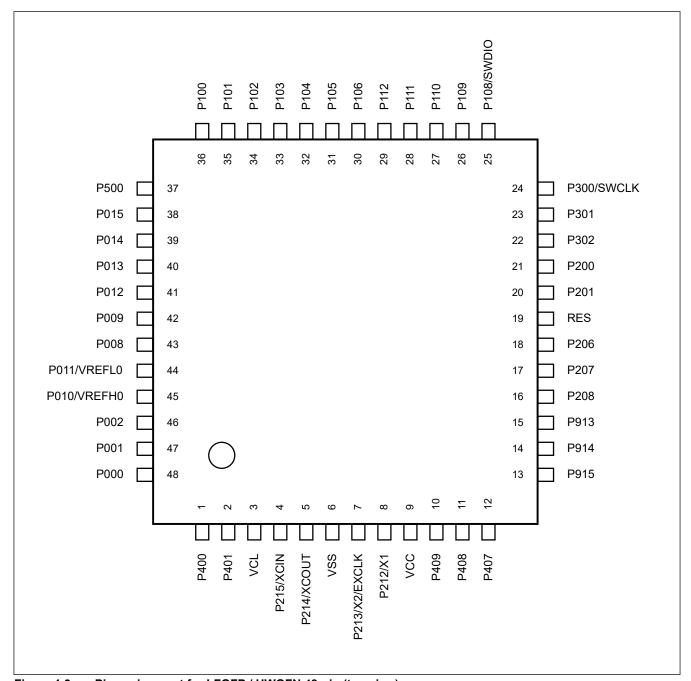


Figure 1.3 Pin assignment for LFQFP / HWQFN 48-pin (top view)

Note: For the QFN package product, solder the exposed die pad to the PCB.

The potential of the exposed die pad is recommended to design as electrically open.

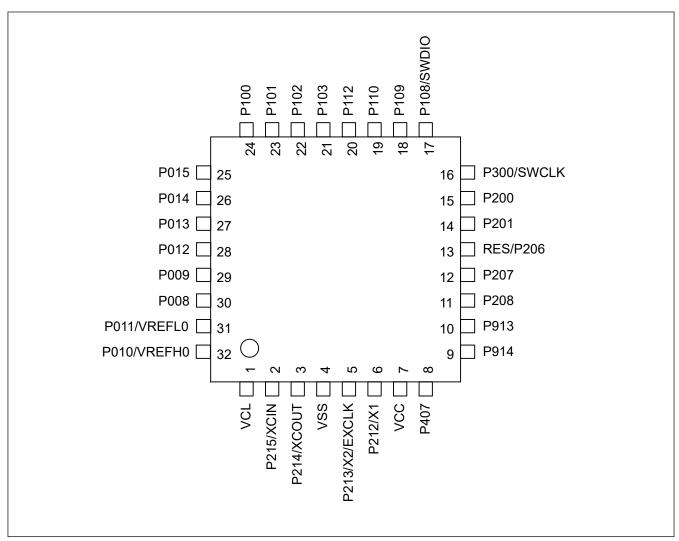


Figure 1.4 Pin assignment for LQFP / HWQFN 32-pin (top view)

Note: For the QFN package product, solder the exposed die pad to the PCB.

The potential of the exposed die pad is recommended to design as electrically open.

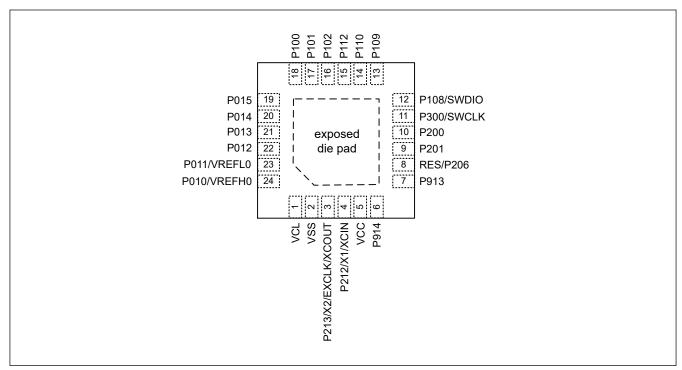


Figure 1.5 Pin assignment for HWQFN 24-pin (top view)

Note: For the QFN package product, solder the exposed die pad to the PCB.

The potential of the exposed die pad is recommended to design as electrically open.

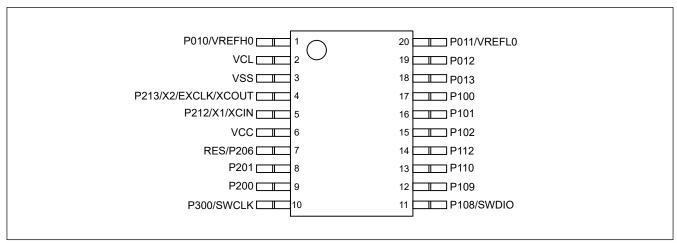


Figure 1.6 Pin assignment for LSSOP 20-pin (top view)

1.7 Pin Lists

Table 1.15 Pin list (1 of 3)

Pin	numb	er					Timers		Commun	ication int	erfaces	Analogs	НМІ	
48- pin	32- pin	24- pin	20- pin	Power, System, Clock, Debug	I/O ports	Interrupt	TAU	RTC	SAU	UARTA	IICA	ADC	стѕи	CCD
1	_	_	_	_	P400	_	_	_	_	_	SCLA1_ D	_	_	CCD7
2	_	_	_	_	P401	_	_	_	_	_	SDAA1_ D	_	_	CCD6
3	1	1	2	VCL	_	_	_	_	_	_	_	_	_	_
4	2	_	_	XCIN	P215	_	_	_	_	_	_	_	_	_
5	3	_	_	XCOUT	P214	_	_	_	_	_	_	_	_	_
6	4	2	3	VSS	_	_	_	_	_	_	_	_	_	
7	5	3	4	X2/ EXCLK/ XCOUT *1	P213	IRQ0_B	TI00_A/ TI02_B/ TO02_B	_	TXD1_A / SO11_A	TXDA0_ B	SDAA0_ B	_	_	
8	6	4	5	X1/ XCIN*1	P212	IRQ1_B	TO00_A /TI03_C/ TO03_C	_	RXD1_A /SI11_A/ SDA11_ A	RXDA0_ B	SCLA0_ B	_	_	
9	7	5	6	VCC	_	_	_	_	_	_	_	_	_	_
10	_	_	_	_	P409	IRQ6_B	TI03_E/ TO03_E	_	SCK11_ C/ SCL11_ C	_	_	_	_	
11	_	_	_	_	P408	IRQ7_B	TI04_C/ TO04_C	_	_	_	SCLA1_ F	_	_	_
12	8	_		PCLBUZ 0_C	P407	IRQ4_C	_	RTCOU T_A	SCK11_ A/ SCL11_ A	_	SDAA1_ F*3	_	_	
13	_	_	_	_	P915	_	_	_	SO01_B	_	_	_	_	_
14	9	6	_	_	P914	_	_	_	_	_	SCLA0_ A	_	_	CCD5
15	10	7	_	_	P913	_	_	_	_	_	SDAA0_ A	_	_	CCD4
16	11	_	_	_	P208	IRQ3_C	TI00_B	_	SCK01_ B*3/ SCL01_ B	TXDA0_ A	SDAA1_ A	_	_	
17	12	_	_	_	P207	IRQ2_C	TO00_B	_	SI01_B *3/ SDA01_ B	RXDA0_ A	SCLA1_ A	_	_	_
18	_	_		_	P206	IRQ0_C	_	_	_	_	_	_	_	_
19	13	8	7	RES	P206*2	_	_	_	_	_	_	_	_	_
20	14	9	8	PCLBUZ 0_A	P201	IRQ5_B	TI05_B/ TO05_B	RTCOU T_B	SCK11_ B/ SCL11_ B/ SSI00_B	_	_	_	_	_

Table 1.15 Pin list (2 of 3)

Pin	numb	er		-			Timers		Commun	ication int	terfaces	Analogs	НМІ	
48- pin	32- pin	24- pin	20- pin	Power, System, Clock, Debug	I/O ports	Interrupt	TAU	RTC	SAU	UARTA	IICA	ADC	стѕи	CCD
21	15	10	9	_	P200	IRQ0_A/N MI	_	_	_	_	_	_	_	
22	_	_	_	_	P302	IRQ0_D	TI05_C/ TO05_C	_	SCL21_ A	TXDA1_ C	SDAA1_ C	_	TS0	_
23	_	_	_	_	P301	IRQ6_A	TI06_B/ TO06_B	_	SDA21_ A	RXDA1_ C	SCLA1_ C	_	TS1	_
24	16	11	10	SWCLK	P300	_	TI04_B/ TO04_B	_	_	_	_	_	_	_
25	17	12	11	SWDIO	P108	_	TI03_B/ TO03_B	_	_	_	_	_	_	_
26	18	13	12	PCLBUZ 1_B	P109	IRQ4_B	TI02_A/ TO02_A	_	TXD2_A / SO20_A	TXDA0_ C	SDAA0_ C	_	TS2	CCD3
27	19	14	13	_	P110	IRQ3_B	TI01_A/ TO01_A	_	RXD2_A /SI20_A/ SDA20_ A	RXDA0_ C	SCLA0_ C	_	TS3	CCD2
28	_		_	_	P111	IRQ1_C	TI07_B/ TO07_B	_	_	_	_	_	TS4	_
29	20	15	14	_	P112	IRQ2_B	TI03_A/ TO03_A	_	SCK20_ A/ SCL20_ A/ SSI00_ C	_	_	_	TSCAP	_
30	_	_		_	P106	IRQ0_E	_	_	SO10_A	TXDA1_ B	_	_	TS5	_
31	_	_	_	_	P105	IRQ1_D	TI01_D/ TO01_D / TO00_D	_	SI10_A/ SDA10_ A	RXDA1_ B	_	_	TS6	_
32	_	_		_	P104	IRQ6_C	TI02_D/ TO02_D / TI00_D	_	SCK10_ A/ SCL10_ A	_	_	_	TS7	_
33	21		_	_	P103	IRQ5_A	TI05_A/ TO05_A	_	SSI00_A	TXDA1_ A	SDAA1_ B	_	TS8	_
34	22	16	15	PCLBUZ 0_B	P102	IRQ4_A	TI06_A/ TO06_A / TO00_C	RTCOU T_C	SCK00_ A/ SCL00_ A	RXDA1_ A	SCLA1_ B	_	TS9	_
35	23	17	16	_	P101	IRQ3_A	TI07_A/ TO07_A / TI00_C	_	TXD0_A / SO00_A	TXDA0_ D	SDAA0_ D/ SDAA1_ G	AN021	TS10	CCD1
36	24	18	17	_	P100	IRQ2_A	TI04_A/ TO04_A / TI01_B/ TO01_B	_	RXD0_A /SI00_A/ SDA00_ A	RXDA0_	SCLA0_ D/ SCLA1_ G	AN022	TS11	CCD0
37	-	_	_	_	P500	_	TI03_D/ TO03_D	_	_	_	_	_	TS12	_

Table 1.15 Pin list (3 of 3)

Pin	numb	er					Timers		Commun	ication int	erfaces	Analogs	НМІ	
48- pin	32- pin	24- pin	20- pin	Power, System, Clock, Debug	I/O ports	Interrupt	TAU	RTC	SAU	UARTA	IICA	ADC	стѕи	CCD
38	25	19	_	_	P015	IRQ1_A	_	_	_	_	_	AN007	TS13	_
39	26	20	_	_	P014	_	_	_	_	_	_	AN006	TS14	_
40	27	21	18	_	P013	_	_	_	_	_	_	AN005	TS15	_
41	28	22	19	_	P012	_	_	_	_	_	_	AN004	TS16	_
42	29	_	_	_	P009	_	_	_	_	_	_	AN003	TS17	_
43	30	_	_	_	P008	_	_	_	_	_	_	AN002	TS18	_
44	31	23	20	VREFL0	P011	_	_	_	_	_	_	AN001	TS19	_
45	32	24	1	VREFH0	P010	_	_	_	_	_	_	AN000	TS20	_
46	_	_	_	_	P002	IRQ7_C	_	_	_	_	_	AN010	TS21	_
47	_	_	_	_	P001	IRQ7_A	_	_	_	_	_	AN009	TS22	_
48	_	_	_	_	P000	IRQ6_D	_	_	_	_	_	AN008	TS23	_

Note 1. Available when setting CMC.XTSEL = 1 for 24-pin and 20-pin products.

Note: Some signal names have _A, _B, _C, _D, _E, _F, or _G suffixes, but these suffixes can be ignored when assigning functionality, except for SAU and IICA. For SAU and IICA, only signals, except for SCK11, SCL11 and SSI00, bearing the same suffix can be selected. Assigning the same function to two or more pins simultaneously is prohibited.

Note 2. Available only in 32-pin, 24-pin, and 20-pin products.

Note 3. Available only in 48-pin products.

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

$$VCC^{*1} = VREFH0 = 1.6 \text{ to } 5.5 \text{ V}$$

$$VSS = VREFL0 = 0 V, Ta = T_{opr}$$

Note 1. The typical condition is set to VCC = 3.3 V.

Figure 2.1 shows the timing conditions.

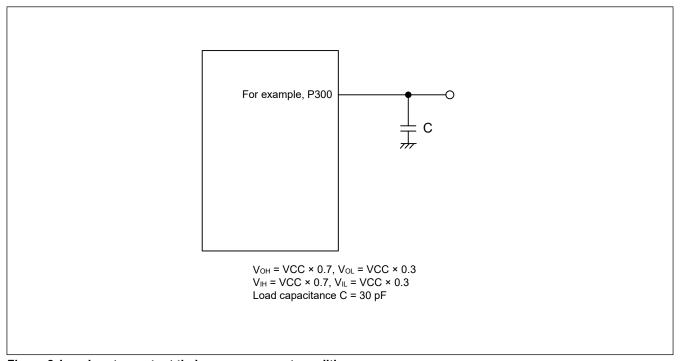


Figure 2.1 Input or output timing measurement conditions

2.1 Absolute Maximum Ratings

Table 2.1 Absolute maximum ratings (1 of 2)

Parameter		Symbol	Value	Unit
Power supply voltage		VCC	-0.5 to +6.5	V
VCL pin input voltage		V _{IVCL}	-0.3 to +2.1 and -0.3 to VCC + 0.3*1	V
Input voltage	P100 to P106, P108 to P112, P200, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915, RES	V _I 1	-0.3 to VCC + 0.3*2	V
	P400, P401, P913, P914 (5 V tolerant)	V _I 2	-0.3 to +6.5	V
	P000 to P002, P008 to P015, P212 to P215	V _I 3	-0.3 to VCC + 0.3*2	V
Output voltage	P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915	V _O 1	-0.3 to VCC + 0.3*2	V
	P400, P401, P913, P914 (N-ch open-drain)	V _O 2	-0.3 to +6.5	V
	P000 to P002, P008 to P015, P212, P213	V _O 3	-0.3 to VCC + 0.3*2	V
Analog input voltage	AN000 to AN010	V _{AI} 1	-0.3 to VCC + 0.3 and -0.3 to VREFH0 + 0.3*2 *3	V
	AN021 to AN022	V _{Al} 2	-0.3 to VCC + 0.3 and -0.3 to VREFH0 + 0.3*2 *3	V

Table 2.1 Absolute maximum ratings (2 of 2)

Parameter			Symbol	Value	Unit
High-level output current		Per pin	I _{OH} 1	-40	mA
	P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915	Total of all pins		-100	mA
	P000 to P002, P008 to	Per pin	I _{OH} 2	-5	mA
	P015, P212, P213	Total of all pins		-20	mA
Low-level output current	P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P400, P401, P407 to P409, P500, P913 to P915	Per pin	I _{OL} 1	40	mA
	P400, P401	Total of all pins		70	mA
	P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P913 to P915			100	mA
	P000 to P002, P008 to	Per pin	I _{OL} 2	10	mA
	P015, P212, P213	Total of all pins		20	mA
Ambient operating temperature	In normal operation mod	e	Та	-40 to +105 -40 to +125	°C
	In flash memory programming mode			-40 to +105 -40 to +125	°C
Storage temperature			Tstg	-65 to +150	°C

Note 1. Connect the VCL pin to VSS via a capacitor (0.47 to 1 μF). The listed value is the absolute maximum rating of the VCL pins. Only use the capacitor connection. Do not apply a specific voltage to this pin.

Note: The characteristics of functions multiplexed on a given pin are the same as those for the port pin unless otherwise specified.

Note: VREFH0 refers to the positive reference voltage of the A/D converter.

Note: The reference voltage is VSS.

Caution: Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Table 2.2 Recommended operating conditions

Parameter	Symbol	Min	Тур	Max	Unit	
Power supply voltages	vcc	1.6	_	5.5	٧	
	VSS	_	0	_	٧	
Analog power supply voltages	VREFH0	When used as ADC12 Reference	1.6	_	VCC	٧
	VREFL0	_	0	_	V	

Note 2. This voltage must be no higher than 6.5 V.

Note 3. The voltage on a pin in use for A/D conversion must not exceed VREFH0 + 0.3.

2.1.1 Tj/Ta Definition

Table 2.3 Tj/Ta definition

Conditions: Products with operating temperature Ta = -40 to +125°C

Parameter	Symbol	Тур	Max*1	Unit	Test conditions
Permissible junction temperature	Тј	_	140 125	°C	High-speed mode Middle-speed mode Low-speed mode Subosc-speed mode

Note 1. The upper limit of operating temperature is 105°C or 125°C depending on the product. For details, see section 1.3. Part Numbering. If the part number shows the operation temperature at 105°C, then the maximum value of Tj is 125°C, otherwise it is 140°C.

Note: Make sure that Tj = T_a + θ ja × total power consumption (W), where total power consumption = (VCC - V_{OH}) × Σ I_{OH} + V_{OL} × Σ I_{OL} + I_{CC}max × VCC.

2.2 Oscillators Characteristics

2.2.1 Main clock Oscillator Characteristics

Table 2.4 Main clock oscillator characteristics

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter	Parameter					Test conditions
Main clock oscillation allowable input cycle time*1	Ceramic resonator Crystal resonator	0.05	_	1	μs	_

Note 1. The listed time and frequency indicate permissible ranges of the oscillator. For actual applications, request evaluation by the manufacturer of the oscillator circuit mounted on a board so you can use appropriate values. Refer to AC Characteristics for instruction execution time.

Note: Since the CPU is started by the high-speed on-chip oscillator clock after release from the reset state, the user should use the oscillation stabilization time counter status register (OSTC) to check the X1 clock oscillation stabilization time. Specify the values for the oscillation stabilization time in the OSTC register and the oscillation stabilization time select register (OSTS) after having sufficiently evaluated the oscillation stabilization time with the resonator to be used.

2.2.2 Sub-clock Oscillator Characteristics

Table 2.5 Sub-clock oscillator characteristics

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V

Parameter				Тур	Max	Unit	Test conditions
Sub-clock oscillation frequency $(f_{SOSC})^{*1}$	Crystal resonator	CMC.XTS EL = 0	_	32.768	_	kHz	Ta = -40 to +125°C, 1.6 V ≤ VCC ≤ 5.5 V
		CMC.XTS EL = 1					Ta = -40 to +105°C, 2.4 V ≤ VCC ≤ 5.5 V

Note 1. The listed time and frequency indicate permissible ranges of the oscillator. For actual applications, request evaluation by the manufacturer of the oscillator circuit mounted on a board so you can use appropriate values. Refer to AC Characteristics for instruction execution time.

2.2.3 On-chip Oscillators Characteristics

Table 2.6 On-chip oscillators characteristics (1 of 2)

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions	
High-speed on-chip of	f _{HOCO}	1	_	32	MHz	_	
High-speed on-chip oscillator clock	OSCSF.HOCOSF = 1	_	-1.0	_	+1.0	%	Ta = -40 to +125°C, 1.6 V ≤ VCC ≤ 5.5 V
frequency accuracy	OSCSF.HOCOSF = 0*3	_	-15	_	0	%	_

Table 2.6 On-chip oscillators characteristics (2 of 2)

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
High-speed on-chip oscillator clock frequency trimming resolution	_	_	0.05	_	%	_
High-speed on-chip oscillator clock oscillation stabilization time*4	t _{HOCO}	_	_	4.4	μs	_
Middle-speed on-chip oscillator clock frequency*1	f _{MOCO}	1	_	4	MHz	_
Middle-speed on-chip oscillator clock frequency accuracy	_	-12	_	12	%	_
Middle-speed on-chip oscillator clock frequency trimming resolution	_	_	0.15	_	%	_
Middle-speed on-chip oscillator clock oscillation stabilization time	t _{MOCO}	_	_	1	μs	_
Middle-speed on-chip oscillator frequency temperature coefficient	_	_	_	±0.17*2	%/°C	_
Low-speed on-chip oscillator clock frequency*1	f _{LOCO}	_	32.768	_	kHz	_
Low-speed on-chip oscillator clock frequency accuracy	_	-15	_	15	%	_
Low-speed on-chip oscillator clock frequency trimming resolution	_	_	0.3	_	%	_
Low-speed on-chip oscillator clock oscillation stabilization time	t _{LOCO}	_	_	100	μs	_
Low-speed on-chip oscillator frequency temperature coefficient	_	_	_	±0.21*2	%/°C	_

Note 1. The listed values only indicate the characteristics of the oscillators. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

Note 2. These values are the results of characteristic evaluation and are not checked for shipment.

Note 3. The listed condition applies when OFS1.HOCOFRQ1[2:0] = 010b.

Note 4. Check OSCSF.HOCOSF to confirm whether stabilization time has elapsed.

2.3.1 Pin Characteristics

Table 2.7 I/O I_{OH}

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to ± 125 °C

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions																																						
Allowable high-level output current*1	Per pin for P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915	I _{OH} 1	_	_	-10 ^{*2}	mA	1.6 V ≤ VCC ≤ 5.5 V																																						
	Total of all pins		_	_	-80 ^{*4}	mA	4.0 V ≤ VCC ≤ 5.5 V																																						
	(when duty ≤ 70% ^{*3})		_	_	-19	mA	2.7 V ≤ VCC < 4.0 V																																						
			_	_	-10	mA	1.8 V ≤ VCC < 2.7 V																																						
			_	_	-5	mA	1.6 V ≤ VCC < 1.8 V																																						
	Per pin for P000 to P002, P008 to P015, P212, P213	I _{OH} 2	<u> </u>	-3 ^{*2}	mA	4.0 V ≤ VCC ≤ 5.5 V																																							
		_	_	_	-1 ^{*2}	mA	2.7 V ≤ VCC < 4.0 V																																						
			_	_	-1 ^{*2}	mA	1.8 V ≤ VCC < 2.7 V																																						
											_	_	-0.5 ^{*2}	mA	1.6 V ≤ VCC < 1.8 V																														
	Total of all pins													1	1	1							1	1	1	1	_	_	-20	mA	4.0 V ≤ VCC ≤ 5.5 V														
	(when duty ≤ 70%*3)		_	_	-10	mA	2.7 V ≤ VCC < 4.0 V																																						
																																								_	_	_	-5	mA	1.8 V ≤ VCC < 2.7 V
			_	_	-5	mA	1.6 V ≤ VCC < 1.8 V																																						

- Note 1. Device operation is guaranteed at the listed currents even if current is flowing from the VCC pin to an output pin.
- Note 2. The combination of these and other pins must also not exceed the value for maximum total current.
- Note 3. The listed currents apply when the duty cycle is no greater than 70%. Use the following formula to calculate the output current when the duty cycle is greater than 70%, where n is the duty cycle.
 - Total output current from the listed pins = (I_{OH} × 0.7)/(n × 0.01) Example when n = 80% and I_{OH} = -10.0 mA
 - Total output current from the listed pins = $(-10.0 \times 0.7)/(80 \times 0.01) = -8.75$ mA

Note that the duty cycle has no effect on the current that is allowed to flow into a single pin. A current higher than the absolute maximum rating must not flow into a single pin.

- Note 4. The maximum value is -50 mA with an ambient operating temperature range of 85°C to 125°C.
- Note: The following pins are not capable of the output of high-level signals in the N-ch open-drain mode.

P100 to P106, P109 to P112, P201, P206 to P208, P212, P213, P407 to P409, P500, and P915

Table 2.8 I/O IOI

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions																																						
Allowable low-level output current*1	Per pin for P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915	I _{OL} 1	_	_	20*2	mA	_																																						
	Per pin for P400, P401, P913, P914		_	_	15 ^{*2}	mA	_																																						
	Total of P400, P401		_	_	70 ^{*4}	mA	4.0 V ≤ VCC ≤ 5.5 V																																						
	(when duty ≤ 70% ^{*3})			_	_	15	mA	2.7 V ≤ VCC < 4.0 V																																					
				_	_	9	mA	1.8 V ≤ VCC < 2.7 V																																					
				_	_	4.5	mA	1.6 V ≤ VCC < 1.8 V																																					
	Total of P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P913 to P915 (when duty ≤ 70%*3)		_	_	80*4	mA	4.0 V ≤ VCC ≤ 5.5 V																																						
			_	_	35	mA	2.7 V ≤ VCC < 4.0 V																																						
			_		20	mA	1.8 V ≤ VCC < 2.7 V																																						
			_	-	10	mA	1.6 V ≤ VCC < 1.8 V																																						
	Total of all pins (when duty ≤ 70% ^{*3})		_	_	150 ^{*5}	mA	1.6 V ≤ VCC ≤ 5.5 V																																						
	Per pin for P000 to P002,	I _{OL} 2	_		8.5 ^{*2}	mA	4.0 V ≤ VCC ≤ 5.5 V																																						
	P008 to P015, P212, P213							_	_	1.5 ^{*2}	mA	2.7 V ≤ VCC < 4.0 V																																	
																						_	_	0.6*2	mA	1.8 V ≤ VCC < 2.7 V																			
																												_	_	0.4*2	mA	1.6 V ≤ VCC < 1.8 V													
	Total of all pins		_	_	20	mA	4.0 V ≤ VCC ≤ 5.5 V																																						
	(when duty ≤ 70%*3)														_			-				_			_													_			_	_	20	mA	2.7 V ≤ VCC < 4.0 V
																																										-	_	_	15
			_	-	10	mA	1.6 V ≤ VCC < 1.8 V																																						

- Note 1. Device operation is guaranteed at the listed currents even if current is flowing from an output pin to VSS pin.
- Note 2. The combination of these and other pins must also not exceed the value for maximum total current.
- Note 3. The listed currents apply when the duty cycle is no greater than 70%. Use the following formula to calculate the output current when the duty cycle is greater than 70%, where n is the duty cycle.
 - Total output current from the listed pins = (I_{OL} × 0.7)/(n × 0.01)
 Example when n = 80% and I_{OL} = 10.0 mA
 - Total output current from the listed pins = $(10.0 \times 0.7)/(80 \times 0.01) = 8.75$ mA
 - Note that the duty cycle has no effect on the current that is allowed to flow into a single pin.
 - A current higher than the absolute maximum rating must not flow into a single pin.
- Note 4. The maximum value is 40 mA with an ambient operating temperature range of 85°C to 125°C.
- Note 5. The maximum value is 80 mA with an ambient operating temperature range of 85°C to 125°C.

Table 2.9 I/O V_{IH}, V_{IL}

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Input voltage, high	P100 to P106, P108 to P112, P200, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915, RES	Normal input buffer	V _{IH} 1	VCC × 0.8		VCC	V	_
	P100 to P106,	TTL input buffer	V _{IH} 2	2.2 — VCC	٧	4.0 V ≤ VCC ≤ 5.5 V		
	P108 to P112, P201, P206 to			2.0	_	VCC	V	3.3 V ≤ VCC < 4.0 V
	P208, P300 to P302, P407 to P409, P500, P915			1.5	_	VCC	V	1.6 V ≤ VCC < 3.3 V
	P000 to P002, P0	08 to P015	V _{IH} 3	VCC × 0.7	_	VCC	٧	_
	P400, P401, P913	V _{IH} 4	VCC × 0.7	_	6.0	٧	_	
	P212 to P215	V _{IH} 5	VCC × 0.8	_	VCC	V	_	
Input voltage, low	P100 to P106, P108 to P112, P200, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915, RES	Normal input buffer	V _{IL} 1	0	_	VCC × 0.2	V	_
	P100 to P106,	TTL input buffer	V _{IL} 2	0	_	0.8	V	4.0 V ≤ VCC ≤ 5.5 V
	P108 to P112, P201, P206 to			0	_	0.5	V	3.3 V ≤ VCC < 4.0 V
	P208, P300 to P302, P407 to P409, P500, P915			0	_	0.32	V	1.6 V ≤ VCC < 3.3 V
	P000 to P002, P0	P000 to P002, P008 to P015			_	VCC × 0.3	V	_
	P400, P401, P913	P400, P401, P913, P914			_	VCC × 0.3	V	_
	P212 to P215	P212 to P215			_	VCC × 0.2	V	_

Note: The maximum value of V_{IH} of pins P100 to P106, P109 to P112, P201, P206 to P208, P212, P213, P407 to P409, P500, and P915 is VCC, even in the N-ch open-drain mode.

Table 2.10 I/O V_{OH} , V_{OL}

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions																										
Output voltage, high	P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302,	V _{OH} 1	VCC - 1.5	_	_	V	4.0 V ≤ VCC ≤ 5.5 V I _{OH} 1 = -10 mA																										
	P407 to P409, P500, P915		VCC - 0.7	_	_	V	4.0 V ≤ VCC ≤ 5.5 V I _{OH} 1 = -3 mA																										
			VCC - 0.6	_	_	V	2.7 V ≤ VCC ≤ 5.5 V I _{OH} 1 = -2 mA																										
					VCC - 0.5	_	_	V	1.8 V ≤ VCC ≤ 5.5 V I _{OH} 1 = -1.5 mA																								
			VCC - 0.5	_	_	V	1.6 V ≤ VCC ≤ 5.5 V I _{OH} 1 = -1 mA																										
	P000 to P002, P008 to P015, P212, P213	V _{OH} 2	VCC - 0.7	_	_	V	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$ $I_{OH}2 = -3 \text{ mA}$																										
			VCC - 0.5	_	_	V	2.7 V ≤ VCC < 4.0 V I _{OH} 2 = -1 mA																										
						VCC - 0.5	_	_	V	1.8 V ≤ VCC < 2.7 V I _{OH} 2 = -1 mA																							
			VCC - 0.5	_	_	V	1.6 V ≤ VCC < 1.8 V I _{OH} 2 = -0.5 mA																										
Output voltage, low	P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302,	V _{OL} 1	_	_	1.3	V	4.0 V ≤ VCC ≤ 5.5 V I _{OL} 1 = 20 mA																										
	P407 to P409, P500, P915		_	_	0.7	V	4.0 V ≤ VCC ≤ 5.5 V I _{OL} 1 = 8.5 mA																										
			_	_	0.6	V	2.7 V ≤ VCC ≤ 5.5 V I _{OL} 1 = 3 mA																										
			_	_	0.4	V	2.7 V ≤ VCC ≤ 5.5 V I _{OL} 1 = 1.5 mA																										
			_	_	0.4	V	1.8 V ≤ VCC ≤ 5.5 V I _{OL} 1 = 0.6 mA																										
			_	_	0.4	V	1.6 V ≤ VCC ≤ 5.5 V I _{OL} 1 = 0.3 mA																										
	P000 to P002, P008 to P015, P212, P213	V _{OL} 2	_	_	0.7	V	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$ $I_{OL}2 = 8.5 \text{ mA}$																										
					_	_	0.5	V	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V}$ $I_{OL}2 = 1.5 \text{ mA}$																								
								_	_	0.4	V	$1.8 \text{ V} \le \text{VCC} < 2.7 \text{ V}$ $I_{OL}2 = 0.6 \text{ mA}$																					
			_	_	0.4	V	1.6 V ≤ VCC < 1.8 V I _{OL} 2 = 0.4 mA																										
	P400, P401, P913, P914	V _{OL} 3	_	_	2.0	V	4.0 V ≤ VCC ≤ 5.5 V I _{OL} 3 = 15 mA																										
																													_	_	0.4	V	4.0 V ≤ VCC ≤ 5.5 V I _{OL} 3 = 5 mA
												_	_	0.4	V	1.8 V ≤ VCC ≤ 5.5 V I _{OL} 3 = 2 mA																	
					0.4	V	1.6 V ≤ VCC ≤ 5.5 V I _{OL} 3 = 1 mA																										

Note: P100 to P106, P109 to P112, P201, P206 to P208, P212, P213, P407 to P409, P500, and P915 do not output high-level signals in the N-ch open-drain mode.

Note: The characteristics of functions multiplexed on a given pin are the same as those for the port pin unless otherwise specified.

Table 2.11 I/O controlled current drive port characteristics

Conditions: VCC = 2.7 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Output current, low	P100, P101, P109,	CCSn.S	0-		1.8	2.6	mA	4.0 V ≤ VCC ≤ 5.5 V
	P110, P400, P401, P913, P914	ET[2:0] = 0x01 CCSn.S ET[2:0] = 0x02 CCSn.S ET[2:0] = 0x03		0.8	1.5	2.3		2.7V ≤ VCC < 4.0 V
	ET[2:			3.0	4.9	6.5		4.0 V ≤ VCC ≤ 5.5 V
				2.7	4.3	5.9		3.0 V ≤ VCC < 4.0 V
			T[2:0]	6.6	10.0	13.2		4.0 V ≤ VCC ≤ 5.5 V
				6.0	9.1	12.1		3.3 V ≤ VCC ≤ 5.5 V
	P400, P401, P913, P914			10.2	15.0	19.8	, F	4.0 V ≤ VCC ≤ 5.5 V
		ET[2:0] = 0x04		9.4	13.8	18.2		3.3 V ≤ VCC < 4.0 V

Note: n = 0 to 7

Note: The listed currents apply when the output current control function is enabled.

Table 2.12 I/O other characteristics

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions	
Input leakage current, high	P100 to P106, P108 to P112, P200, P201, P206 to P208, P300 to P302, P400, P401, P407 to P409, P500, P915, RES	I _{LIH} 1		_	1	μΑ	V _I = VCC	
	P000 to P002, P008 to P015	I _{LIH} 2	_	_	1	μΑ	V _I = VCC	
	P212 to P215	I _{LIH} 3	_	<u> </u>	1	μΑ	V _I = VCC	
Input leakage current, low	P100 to P106, P108 to P112, P200, P201, P206 to P208, P300 to P302, P400, P401, P407 to P409, P500, P915, RES	I _{LIL} 1	_	_	-1	μΑ	V _I = VSS	
	P000 to P002, P008 to P015	I _{LIL} 2	_	_	-1	μΑ	V _I = VSS	
	P212 to P215	I _{LIL} 3	-	_	-1	μΑ	V _I = VSS	
On-chip pull-up resistance	P100 to P106, P108 to P112, P201, P206 to P208, P300 to P302, P407 to P409, P500, P915, RES	R _U	10	20	100	kΩ	V _I = VSS In input port	
Input capacitance	P200	Cin			30	pF	Vin = 0 V, f = 1 MHz,	
	Other input pins		_	_	15		Ta = 25°C	

2.3.2 Operating and Standby Current

Table 2.13 Operating and standby current (1) (1 of 2)

Conditions: VCC = 1.6 to 5.5 V

Paramete	r			Symbol	Typ*5	Max	Unit	Test Conditions		
Supply current ^{*1}	High- speed mode*2	Normal mode	All peripheral clocks disabled, CoreMark code executing from flash	ICLK = 32 MHz	loc	2.9	_	mA	_	
			All peripheral clocks enabled, CoreMark code executing from flash*6	ICLK = 32 MHz		_	5.2		_	
		Sleep mode	All peripheral clocks disabled	ICLK = 32 MHz		0.92	_		_	
			All peripheral clocks enabled*6	ICLK = 32 MHz		_	2.8		_	
	Middle-	Normal	All peripheral clocks	ICLK = 24 MHz		2.2	_			
	speed mode*2	mode	disabled, CoreMark code executing	ICLK = 16 MHz		1.6	_		_	
	mode		from flash	ICLK = 8 MHz		1.0	_		_	
				ICLK = 4 MHz		0.70	_		_	
			All peripheral clocks	ICLK = 24 MHz		_	4.0		_	
			enabled, CoreMark code executing	ICLK = 16 MHz		_	2.8		_	
				ICLK = 8 MHz		_	1.7	†	_	
				ICLK = 4 MHz		— 1.1		_		
		Sleep	All peripheral clocks	ICLK = 24 MHz		0.75	_		_	
		mode	disabled	ICLK = 16 MHz		0.65	_		_	
				ICLK = 8 MHz		0.52	_		_	
				ICLK = 4 MHz		0.46	_		_	
			All peripheral clocks	ICLK = 24 MHz		_	2.2		_	
			enabled*6	ICLK = 16 MHz		_	1.7		_	
				ICLK = 8 MHz		_	1.1		_	
				ICLK = 4 MHz		_	8.0		_	
	Low- speed mode*3	Normal mode		μΑ	_					
			All peripheral clocks enabled, CoreMark code executing from flash*6		ICLK = 2 MHz		_	342		_
		Sleep mode	All peripheral clocks disabled	ICLK = 2 MHz		56	_		_	
			All peripheral clocks enabled*6	ICLK = 2 MHz		_	172		_	

Table 2.13 Operating and standby current (1) (2 of 2)

Conditions: VCC = 1.6 to 5.5 V

Parametei						Symbol	Typ*5	Max	Unit	Test Conditions
Supply	Subosc-	Normal	Peripheral clocks	ICLK = 32.768 kHz	Ta = -40°C	Icc	3.3	_	μΑ	_
current*1	speed mode*4	mode	disabled		Ta = 25°C]	3.6	_		
	*8				Ta = 50°C]	3.9	_		
					Ta = 70°C	1	4.3	_		
					Ta = 85°C]	4.9	_		
					Ta = 105°C		6.6	_		
					Ta = 125°C		10.9	_		
			Peripheral clocks	ICLK = 32.768 kHz	Ta = -40°C		_	7.1		
			enabled*7		Ta = 25°C		_	7.7		
					Ta = 50°C		_	9.7		
					Ta = 70°C		_	14.0		
					Ta = 85°C		_	22.0		
					Ta = 105°C		_	41.0		
					Ta = 125°C		_	91.0		
		Sleep	Peripheral clocks	ICLK = 32.768 kHz	Ta = -40°C		1.0	_		_
		mode	disabled		Ta = 25°C	┥ —	1.2	_	-	
					Ta = 50°C		1.3	_		
					Ta = 70°C		1.6	_		
					Ta = 85°C		2.0	_		
					Ta = 105°C		3.3	_		
					Ta = 125°C		5.9	_		
			Peripheral clocks	ICLK = 32.768 kHz	Ta = -40°C		_	4.7		
			enabled*7		Ta = 25°C		_	5.1		
			Ta = 50°C		_	7.0	1			
				Ta = 70°C		_	12.0			
					Ta = 85°C			19.0		
					Ta = 105°C		_	37.0		
					Ta = 125°C		_	85.0		

Note 1. Supply current is the total current flowing into VCC. Supply current values apply when internal pull-up MOSs are in the off state and these values do not include output charge/discharge current from any of the pins.

- Note 2. The clock source is high-speed on-chip oscillator (HOCO).
- Note 3. The clock source is middle-speed on-chip oscillator (MOCO).
- Note 4. The clock source is the Sub-clock oscillator (SOSC) and CMC.SODRV[1:0] are 10b (Low power mode 2).
- Note 5. VCC = 3.3 V.
- Note 6. Includes operating current for PCLBUZ, TAU, SAU, and IICA functions only. For other peripheral operating currents, please add the current in Peripheral Functions Supply current in Table 2.15.
- Note 7. Includes operating current for PCLBUZ, TAU and SAU functions only. For other peripheral operating currents, please add the current in Peripheral Functions Supply current in Table 2.15.
- Note 8. The operating conditions under which the sub-clock oscillator can be used are specified separately. For details, see section 2.2.2. Sub-clock Oscillator Characteristics.

Table 2.14 Operating and standby current (2)

Conditions: VCC = 1.6 to 5.5 V

Parame	ter					Symbol	Typ*3	Max	Unit	Test conditions
Supply	Software	Peripheral	PSMCR.RA	All SRAMs	Ta = -40°C	Icc	0.20	1.2	μΑ	_
current *1	Standby mode ^{*2}	modules stop	MSD[1:0] are 00b	(0x2000_4000 to 0x2000_7FFF) are	Ta = 25°C		0.25	1.2]	
				on	Ta = 50°C		0.35	3.0		
					Ta = 70°C		0.60	7.0		
					Ta = 85°C		0.95	14.0		
					Ta = 105°C		2.2	32.0		
					Ta = 125°C		4.6	80.0		
			PSMCR.RA	Only 8 KB SRAM	Ta = -40°C		0.20	1.2		_
			MSD[1:0] are 11b	(0x2000_4000 to 0x2000_5FFF) is on	Ta = 25°C		0.25	1.2		
					Ta = 50°C		0.35	3.0		
					Ta = 70°C		0.55	6.5]	
					Ta = 85°C		0.90	13.0		
					Ta = 105°C		2.0	28.0		
İ					Ta = 125°C		4.3	75.0		

Note 1. Supply current is the total current flowing into VCC. Supply current values apply when internal pull-up MOSs are in the off state and these values do not include output charge/discharge current from any of the pins.

Note 2. The IWDT and LVD are not operating. Note 3. VCC = 3.3 V.

Table 2.15 Peripheral functions supply current

Parameter				Symbol	Typ*12	Max	Unit	Test conditions		
Peripheral Functions	High-speed on cl current*1	hip oscillator operating	OFS1.HOCOFRQ1[2:0] are 010b	Іносо	320	_	μА	_		
Supply current ^{*1}	Middle-speed on	chip oscillator operating	current*1	I _{MOCO}	20	_	μΑ	_		
	Low-speed on ch	nip oscillator operating cu	rrent*1	I _{LOCO}	0.24	_	μΑ	_		
	Main-clock	CMC.MODRV = 0	f _{MOSC} = 10 MHz	I _{MOSC}	160	_	μA	_		
	oscillator	CMC.MODRV = 1	f _{MOSC} = 20 MHz		330	_	μΑ	_		
	Sub-clock oscillator	SBYCR.RTCLPC is	CMC.SODRV[1:0] are 11b (Low power mode 3)	I _{sosc}	0.13	_	μА	_		
			CMC.SODRV[1:0] are 10b (Low power mode 2)		0.34	_	μА	_		
			CMC.SODRV[1:0] are 00b (Low power mode 1)		0.49	_	НА Н	_		
			CMC.SODRV[1:0] are 01b (Normal mode)		0.62	_	μΑ	_		
		SBYCR.RTCLPC is 0	CMC.SODRV[1:0] are 11b (Low power mode 3)		0.30	_	μA			
			CMC.SODRV[1:0] are 10b (Low power mode 2)		0.51	— II	μА			
			CMC.SODRV[1:0] are 00b (Low power mode 1)		0.65	_	μΑ μΑ μΑ μΑ μΑ μΑ μΑ			
			CMC.SODRV[1:0] are 01b (Normal mode)		0.80	_	μА			
	RTC*1*2*3	RTCC0.RTC128EN is	3 0	I _{RTC}	0.006	_	μΑ	μA —		
		RTCC0.RTC128EN is	s 1		0.001	_	μΑ			
	32-bit interval tim	ner operating current*1*2*	4	I _{IT}	0.06	_	μΑ	-		
	Independent wat current*1*2*5	chdog timer operating	f _{LOCO} = 32.768 kHz (typ.)	I _{IWDT}	0.03	_	μA	_		
	A/D converter operating	When conversion at maximum speed	Normal mode, VREFH0 = VCC = 5.0 V	I _{ADC}	0.85	1.6	mA	_		
	current*1*6		Low voltage mode, VREFH0 = VCC = 3.0 V		0.46	0.75	mA	_		
	VREFH0 current	*7	VREFH0 = 5.0 V	I _{ADREF}	68	_	μΑ	_		
	A/D converter int	ernal reference voltage o	current ^{*1}	I _{ADREF}	86	-	μΑ	_		
	Temperature sen	sor operating current*1		I _{TMPS}	100	_	μΑ	_		
	LVD operating cu	ırrent ^{*1}	LVD0 is enabled*8	I _{LVD0}	0.03	_	μА	_		
			LVD1 is enabled ^{*9}	I _{LVD1}	0.03	_	μΑ	_		
	Self-programmin	g operating current*1*10	1	I _{FSP}	_	12.2				
	Data flash rewrite	e operating current*1*11		I _{BGO}	_	12.2	mA	_		
	Operating curren	t of the true random num	uber generator ^{*1}	I _{TRNG}	1.1	_	mA	_		
	DTC		Data transfer to RAM	I _{DTC}	1.82	_	mA	_		
	UARTA (1 ch)		Operation enable @32MHz Baud rate: 153.6 kbps	I _{UARTA}	85	_	μΑ	_		
	CTSU2SLa		Self-capacitance single scan mode	I _{CTSU}	0.76	0.94	mA	_		

Note 1. This current flows into V_{CC} .

Note 2. The listed currents apply when the high-speed on-chip oscillator (HOCO), middle-speed on-chip oscillator (MOCO), and Main clock oscillator (MOSC) are stopped.

Note 3. This current flows into the realtime clock (RTC). It does not include the operating current of the low-speed on-chip oscillator (LOCO) or the Sub-clock oscillator (SOSC).

The supply current of the RA0 microcontrollers is the sum of either Icc, and I_{RTC}.

When the low-speed on-chip oscillator (LOCO) is selected, I_{LOCO} should be included in the supply current.

When the Sub-clock oscillator (SOSC) is selected, I_{SOSC} should be included in the supply current.

Note 4. This current only flows to the 32-bit interval timer. It does not include the operating current of the low-speed on-chip oscillator (LOCO) or Sub-clock oscillator (SOSC).

The supply current of the RA0 microcontrollers is the sum of either Icc and I_{IT}.

When the low-speed on-chip oscillator (LOCO) is selected, I_{LOCO} should be included in the supply current.

When the Sub-clock oscillator (SOSC) is selected, I_{SOSC} should be included in the supply current.

Note 5. This current only flows to the independent watchdog timer. It does not include the operating current of the low-speed on-chip oscillator (LOCO).

The supply current of the RA0 microcontrollers is the sum of either Icc, I_{IWDT} and I_{LOCO}.

Note 6. This current only flows to the A/D converter. The supply current of the RA0 microcontrollers is the sum of lcc and I_{ADC} when the A/D converter is operating or in the SLEEP mode.

Note 7. This current flows into VREFH0.

Note 8. This current only flows to the LVD0 circuit. The supply current of the RA0 microcontrollers is the sum of lcc and I_{LVD0} when the LVD0 circuit is in operation.

Note 9. This current only flows to the LVD1 circuit. The supply current of the RA0 microcontrollers is the sum of Icc and I_{LVD1} when the LVD1 circuit is in operation.

Note 10. This current only flows during self programming.

Note 11. This current only flows while the data flash memory is being rewritten.

Note 12. VCC = 3.3 V.

2.3.3 Thermal Characteristics

The maximum value of junction temperature (Tj) must not exceed the value specified in the section 2.1.1. Tj/Ta Definition.

Tj is calculated by either of the following equations.

- $Tj = Ta + \theta ja \times Total$ power consumption
- $T_i = T_t + \Psi_{it} \times Total power consumption$

Tj : Junction Temperature (°C)

Ta: Ambient Temperature (°C)

Tt: Top Center Case Temperature (°C)

θja: Thermal Resistance of "Junction"-to-"Ambient" (°C/W)

Ψjt: Thermal Resistance of "Junction"-to-"Top Center Case" (°C/W)

- Total power consumption = Voltage × (Leakage current + Dynamic current)
- Leakage current of IO = Σ (IOL × VOL) / Voltage + Σ (|IOH| × |VCC VOH|) / Voltage
- Dynamic current of IO = Σ IO (Cin + Cload) × IO switching frequency × Voltage Cin: Input capacitance

Cload: Output capacitance

Regarding θ ja and Ψ jt, see Table 2.16.

Table 2.16 Thermal resistance

Parameter	Package	Symbol	Value*1	Unit	Test condition
Thermal resistance	48-pin LFQFP	θја	65.6	°C/W	JESD 51-2 and 51-7
	48-pin HWQFN		20.2		compliant
	32-pin LQFP	-	65.3		
	32-pin HWQFN		23.8		
	24-pin HWQFN		24.2		
	20-pin SSOP		60.7		
	48-pin LFQFP	Ψjt	6.31		
	48-pin HWQFN		0.28		
	32-pin LQFP		6.64		
	32-pin HWQFN		0.32		
	24-pin HWQFN		0.32		
	20-pin SSOP		2.69		

Note 1. The values are reference values when the 4-layer board is used. Thermal resistance depends on the number of layers or size of the board. For details, refer to the JEDEC standards.

2.4 AC Characteristics

Table 2.17 AC characteristics (1 of 2)

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions		
Instruction cycle (minimum	Main system clock (FMAIN) operation	High- speed	T _{CY}	0.03125	_	1	μs	1.8 V ≤ VCC ≤ 5.5 V
instruction	(FIVIAIIV) Operation	mode		0.25	_	1	μs	1.6 V ≤ VCC < 1.8 V
execution time)		Middle-		0.04167	_	1	μs	1.8 V ≤ VCC ≤ 5.5 V
		speed mode		0.25	_	1	μs	1.6 V ≤ VCC < 1.8 V
		Low-speed mode		0.5	_	1	μs	1.6 V ≤ VCC ≤ 5.5 V
	Subsystem clock (FSUB)		26.041	30.5	31.3	μs	1.6 V ≤ VCC ≤ 5.5 V	
	mode s	High- speed mode		0.03125	_	1	μs	1.8 V ≤ VCC ≤ 5.5 V
		Middle- speed mode		0.04167	_	1	μs	1.8 V ≤ VCC ≤ 5.5 V
External system c	lock frequency	,	f _{EX}	1.0	_	20.0	MHz	1.8 V ≤ VCC ≤ 5.5 V
				1.0	_	4.0	MHz	1.6 V ≤ VCC < 1.8 V
External system cl width	lock input high-level width,	low-level	t _{EXH} t _{EXL}	24	_	_	ns	1.8 V ≤ VCC ≤ 5.5 V
width				120	_	_	ns	1.6 V ≤ VCC < 1.8 V
TI00 to TI07 input	high-level width, low-level	width	t _{TIH} t _{TIL}	1/f _{MCK} +10*1	_	_	ns	
TO00 to TO07 out	put frequency	High-	f _{TO}	_	_	16 ^{*2}	MHz	4.0 V ≤ VCC ≤ 5.5 V
		speed mode		_	_	8	MHz	2.7 V ≤ VCC < 4.0 V
Middle- speed			_	_	4	MHz	1.8 V ≤ VCC < 2.7 V	
mode					_	2	MHz	1.6 V ≤ VCC < 1.8 V
		Low-speed mode		_		2	MHz	1.6 V ≤ VCC ≤ 5.5 V

Table 2.17 AC characteristics (2 of 2)

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions	
PCLBUZ0, PCLBUZ1 output frequency	High-	f _{PCL}	_	_	16 ^{*2}	MHz	4.0 V ≤ VCC ≤ 5.5 V
 	speed mode Middle- speed mode		_	_	8	MHz	2.7 V ≤ VCC < 4.0 V
			_	_	4	MHz	1.8 V ≤ VCC < 2.7 V
			_	_	2	MHz	1.6 V ≤ VCC < 1.8 V
	Low-speed mode		_	_	2	MHz	1.6 V ≤ VCC ≤ 5.5 V
Interrupt input high-level width, low-level width	NMI/IRQ0, IRQ1 to IRQ7	f _{IRQH} f _{IRQL}	1	_	_	μs	1.6 V ≤ VCC ≤ 5.5 V

Note 1. f_{MCK}: Timer array unit operating clock frequency

To set this operating clock, use the CKS[1:0] bits of the timer mode register 0n (TMR0n).

m: Unit number (m = 0), n: Channel number (n = 0 to 7)

Note 2. The maximum value is 12MHz with an ambient operating temperature range of 105°C to 125°C.

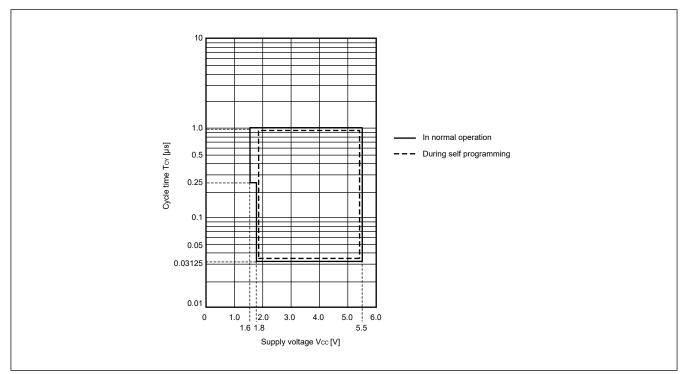


Figure 2.2 T_{CY} vs V_{CC} in High-speed mode

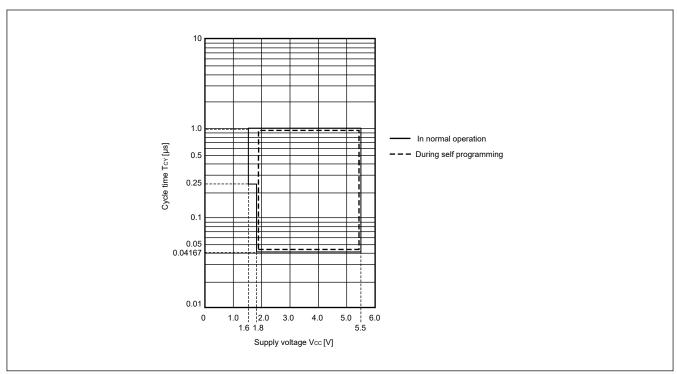


Figure 2.3 T_{CY} vs V_{CC} in Middle-speed mode

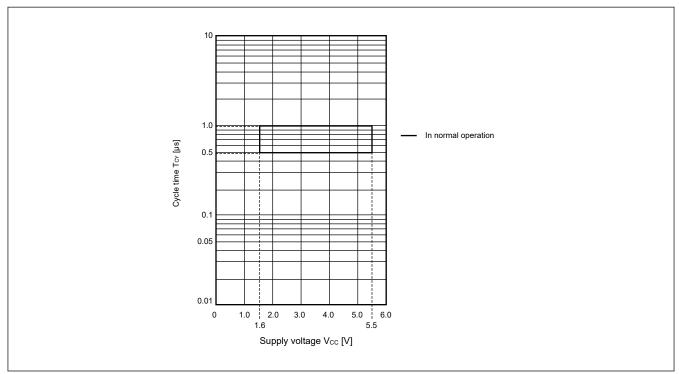


Figure 2.4 T_{CY} vs V_{CC} in Low-speed mode

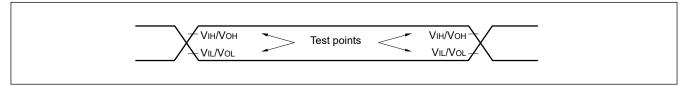


Figure 2.5 AC timing test points

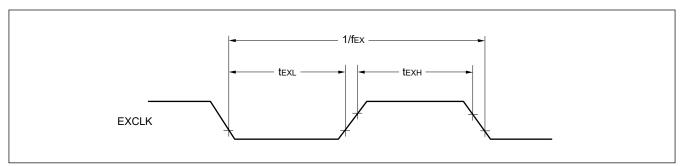


Figure 2.6 External system clock timing

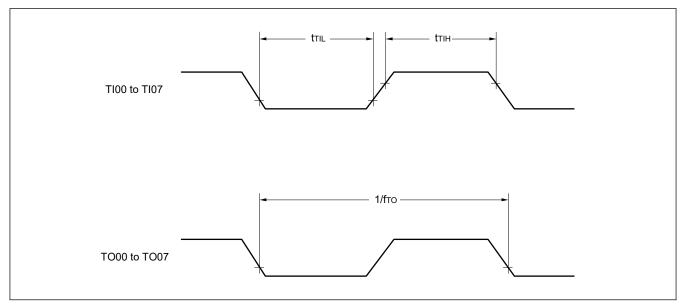


Figure 2.7 TI/TO timing

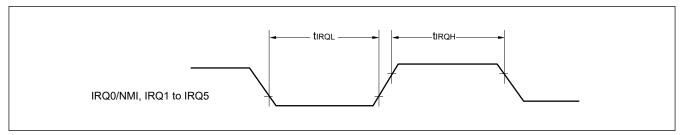


Figure 2.8 IRQ interrupt input timing

2.4.1 Reset Timing

Table 2.18 Reset timing (1 of 2)

Parameter			Min	Тур	Max	Unit	Test conditions
RES pulse width	At power-on*3	t _{RESWP}	9.9	_	_	ms	_
	Not at power-on	t _{RESW}	10	_	_	μs	_
Wait time after RES cancellation	LVD0 enabled*1	t _{RESWT}	_	0.506	0.694	ms	_
(at power-on)	LVD0 disabled*2		_	0.201	0.335	ms	_
Wait time after RES cancellation	LVD0 enabled*1	t _{RESWT2}	_	0.476	0.616	ms	_
(during powered-on state)	LVD0 disabled*2		_	0.170	0.257	ms	_

Table 2.18 Reset timing (2 of 2)

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Internal reset by Independent watch dog timer reset, SRAM parity error reset, software reset	t _{RESW2}	_	0.04	0.041	ms	_

Note 1. When OFS1.LVDAS = 0.

Note 2. When OFS1.LVDAS = 1.

Note 3. When RES pin is not used as the external reset input, this specification can be ignored.

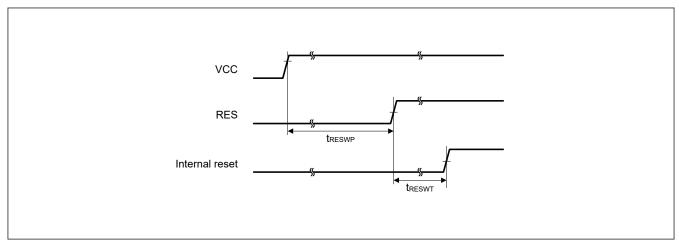


Figure 2.9 Reset input timing at power-on

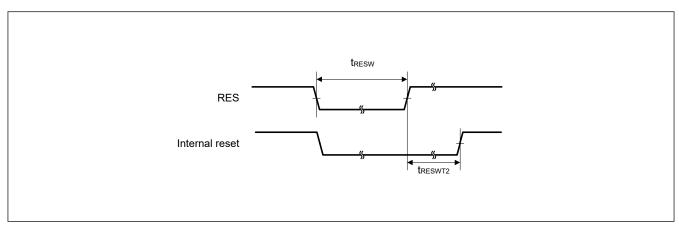


Figure 2.10 Reset input timing (1)

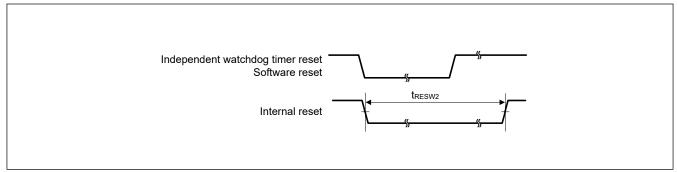


Figure 2.11 Reset input timing (2)

2.4.2 Wakeup Time

Table 2.19 Timing of recovery from low power modes (1)

Parameter				Symbol	Min	Тур	Max	Unit	Test conditions
	High-speed mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (20 MHz)*2 VCC = 1.8 V to 5.5 V	t _{SBYMC}	_	1.64	_	ms	Figure 2.12
			System clock source is main clock oscillator (4 MHz)*2 VCC = 1.6 V to 1.8 V		_	8.19	_	ms	
		External clock input to main clock oscillator	System clock source is main clock oscillator (20 MHz) VCC = 1.8 V to 5.5 V	t _{SBYEX}	_	2.8	2.8	μs	
			System clock source is main clock oscillator (4 MHz) VCC = 1.6 V to 1.8 V		_	13.8	14.0	μs	
		System clock source is HOCO	System clock source is HOCO (32 MHz) VCC = 1.8 V to 5.5 V SBYCR.FWKUP = 0	t _{SBYHO}	t _{SBYHO} — 4.2	4.2	4.6	μs	
			System clock source is HOCO (32 MHz) VCC = 1.8 V to 5.5 V SBYCR.FWKUP = 1		_	0.9	1.1	μs	
			System clock source is HOCO (4 MHz) VCC = 1.6 V to 1.8 V		_	5.2	5.6	μs	
		System clock source is M	OCO (4 MHz)	t _{SBYMO}		3.3	4.2	μs	

Note 1. The division ratio of ICLK is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Note 2. The Oscillation Stabilization Time Select Register (OSTS) is set to 0x05.

Table 2.20 Timing of recovery from low power modes (2)

Parameter				Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time from Software Standby	Middle-speed mode	Crystal resonator connected to main clock	System clock source is main clock oscillator (20 MHz)*2 VCC = 1.8 V to 5.5 V	t _{SBYMC}	_	1.64	_	ms	Figure 2.12
mode*1		oscillator	System clock source is main clock oscillator (4 MHz)*2 VCC = 1.6 V to 1.8 V		_	8.19	_	ms	
		External clock input to main clock oscillator	System clock source is main clock oscillator (20 MHz) VCC = 1.8 V to 5.5 V	t _{SBYEX}	_	2.8	2.8	μs	
			System clock source is main clock oscillator (4 MHz) VCC = 1.6 V to 1.8 V		_	13.8	14.0	μs	
		System clock source is HOCO	System clock source is HOCO (24 MHz) VCC = 1.8 V to 5.5 V	t _{SBYHO}	_ 5.1		5.1 5.5		
			System clock source is HOCO (3 MHz) VCC = 1.6 V to 1.8 V		_	5.6	6.1	μs	
		System clock sou	rce is MOCO (4 MHz)	t _{SBYMO}	_	3.3	4.2	μs	

Note 1. The division ratio of ICLK is the minimum division ratio within the allowable frequency range.

Table 2.21 Timing of recovery from low power modes (3)

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions	
Recovery time from Software Standby mode*1	Low-speed mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (2 MHz)*2	t _{SBYMC}	_	4.1	_	ms	Figure 2.12
			System clock source is main clock oscillator (2 MHz)*2	t _{SBYEX}	_	27.5	28.0	μs	
		System clock sou	rce is MOCO (2 MHz)	t _{SBYMO}	_	6.0	7.5	μs	

Note 1. The division ratio of ICLK is the minimum division ratio within the allowable frequency range.

Table 2.22 Timing of recovery from low power modes (4)

Parameter				Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time	Subosc-speed	System clock	SBYCR.RTCLPC = 0	t _{SBYSC}	_	0.29	0.31	ms	Figure 2.12
from Software Standby mode ^{*1}	mode	source is sub- clock oscillator (32.768 kHz)	SBYCR.RTCLPC = 1		_	0.32	0.34	ms	
		System clock source	e is LOCO (32.768 kHz)	t _{SBYLO}	_	0.29	0.36	ms	

Note 1. The sub-clock oscillator or LOCO itself continues oscillating in Software Standby mode during Subosc-speed mode.

The recovery time is determined by the system clock source.

Note 2. The Oscillation Stabilization Time Select Register (OSTS) is set to 0x05.

The recovery time is determined by the system clock source.

Note 2. The Oscillation Stabilization Time Select Register (OSTS) is set to 0x05.

Crystal resonator frequency is 8 MHz and the MOSC Clock Division Register (MOSCDIV) is set to 0x02.

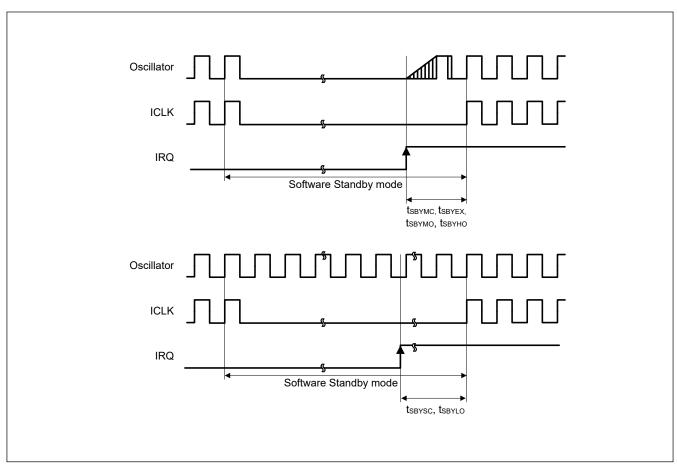


Figure 2.12 Software Standby mode cancellation timing

Table 2.23 Timing of recovery from low power modes (5)

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time from	High-speed	SBYCR.FWKUP = 0	t _{SNZ}	_	4.1	4.4	μs	Figure 2.13
Software Standby mode to Snooze mode	mode System clock source is HOCO	SBYCR.FWKUP = 1		_	0.9	1.0	μs	
	Middle-speed mod System clock sour VCC = 1.8 V to 5.8	rce is HOCO (24 MHz)	t _{SNZ}	_	4.2	4.4	μs	
	Middle-speed mod System clock sour VCC = 1.6 V to 1.8	rce is HOCO (3 MHz)	t _{SNZ}	_	4.8	5.3	μs	
	Low-speed mode System clock soul	rce is MOCO (2 MHz)	t _{SNZ}	_	4.0	5.4	μs	

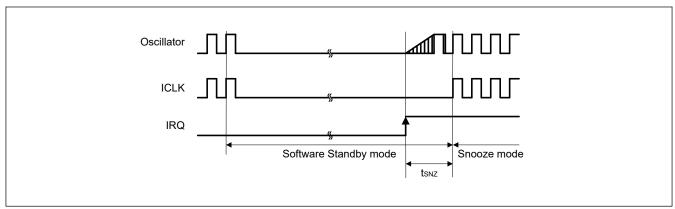


Figure 2.13 Recovery timing from Software Standby mode to Snooze mode

2.5 Peripheral Function Characteristics

2.5.1 Serial Array Unit (SAU)

Table 2.24 In UART communications with devices operating at same voltage levels

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

				High-sp mode	eed	Middle- mode	speed	Low-sp mode	eed		Test
Parameter	arameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
Transfer			_	_	f _{MCK} /6	_	f _{MCK} /6	_	f _{MCK} /6	bps	Figure 2.15
rate ^{*1}		Theoretical value of the maximum transfer rate f_{MCK} = PCLKB*2		_	5.3	_	4	_	0.33	Mbps	

Note 1. The transfer rate in SNOOZE mode is within the range from 4800 to 9600 bps when SBYCR.FWKUP = 0, and within the range from 4800 to 115200 bps when SBYCR.FWKUP = 1.

Note 2. The maximum operating frequencies of the peripheral module clock (PCLKB) are as follows.

High-speed mode: 32 MHz (1.8 V \leq VCC \leq 5.5 V), 4 MHz (1.6 V \leq VCC \leq 5.5 V)

Middle-speed mode: 24 MHz (1.8 V ≤ VCC ≤ 5.5 V), 4 MHz (1.6 V ≤ VCC ≤ 5.5 V)

Low-speed mode: 2 MHz (1.6 V ≤ VCC ≤ 5.5 V)

Note: Select the normal input buffer for the RXDq pin and the normal output mode for the TXDq pin by using the Port gh Pin Function Select Register (PghPFS A.PIM and PghPFS A.NCODR).

gh: Port number (gh = 100, 101, 109, 110, 212, 213)

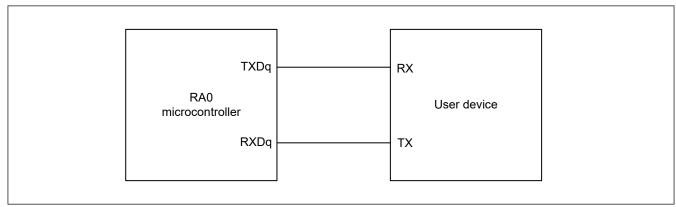


Figure 2.14 Connection in the UART communications with devices operating at same voltage levels

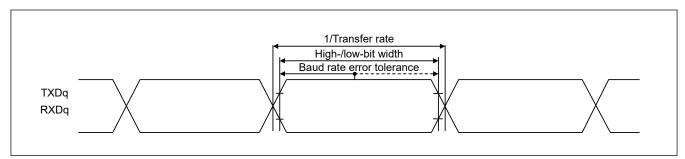


Figure 2.15 Bit width in the UART communications when interfacing devices operate at the same voltage level (reference)

Note: • q: UART number (q = 0 to 2), gh: Port number (qh = 100, 101, 109, 110, 212, 213)

f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, set the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Table 2.25 In simplified SPI communications in the master mode with devices operating at same voltage levels with the internal SCKp clock (the ratings below are only applicable to SPI00)

Conditions: VCC = 2.7 to 5.5 V, VSS = 0 V, Ta = -40 to +85°C

				High-speed mo	de	Middle-speed n	node	Low-speed mod	de		Test
Parameter			Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SCKp cycle time	t _{KCY1} ≥ 2/	4.0 V ≤ VCC ≤ 5.5 V	t _{KCY1}	62.5	_	83.3	_	1000	_	ns	Figure 2.17
	PCLKB	2.7 V ≤ VCC ≤ 5.5 V		83.3	_	125	_	1000	_	ns	Figure 2.18
SCKp high-/ low- level width	4.0 V ≤ VCC ≤ 5.	5 V	t _{KH1} , t _{KL1}	t _{KCY1} /2 - 7	_	t _{KCY1} /2 - 10	_	t _{KCY1} /2 - 50	_	ns	
level width	2.7 V ≤ VCC ≤ 5.	5 V]	t _{KCY1} /2 - 10	_	t _{KCY1} /2 - 15	_	t _{KCY1} /2 - 50	_	ns	
SIp setup time	4.0 V ≤ VCC ≤ 5.	5 V	t _{SIK1}	23	-	33	_	110	_	ns	
(to SCKp↑)*1	2.7 V ≤ VCC ≤ 5.	5 V		33	_	50	_	110	_	ns	
SIp hold time (from SCKp↑)*1	2.7 V ≤ VCC ≤ 5.	5 V	t _{KSI1}	10	_	10	_	10	_	ns	
Delay time from SCKp↓ to SOp output*2	C = 20 pF*3		t _{KSO1}	_	10	_	10	_	10	ns	

- Note 1. The setting applies when SCRmn.DCP0[1:0] = 00b or 11b. The setting for the SIp setup time becomes to SCKp↓ and that for the SIp hold time becomes from SCKp↓ when SCRmn.DCP0[1:0] = 01b or 10b.
- Note 2. This setting applies when SCRmn.DCP0[1:0] = 00b or 11b. The setting for the delay time to SOp output becomes from SCKp↑ when SCRmn.DCP0[1:0] = 01b or 10b.
- Note 3. C is the load capacitance of the SCKp and SOp output lines.

Note: Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR).

Note: • The listed times are only valid when the peripheral I/O redirect function of SPI00 is not in use.

- p: Simplified SPI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), gh: Port number (gh = 100 to 103, 112, 201)
- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00)



Table 2.26 In simplified SPI communications in the master mode with devices operating at same voltage levels with the internal SCKp clock

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

				High-speed m	ode	Middle-speed	mode	Low-speed mo	de		Test
Parameter			Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SCKp cycle time	t _{KCY1} ≥ 4/	2.7 V ≤ VCC ≤ 5.5 V	t _{KCY1}	125	_	166	_	2000	_	ns	Figure 2.17
	PCLKB	2.4 V ≤ VCC ≤ 5.5 V		250	_	250	_	2000	_	ns	Figure 2.18
		1.8 V ≤ VCC ≤ 5.5 V		500	_	500	_	2000	_	ns	
		1.6 V ≤ VCC ≤ 5.5 V		1000	_	1000	_	2000	_	ns	
SCKp high-/ low-level width	4.0 V ≤ VCC ≤ 5.	5 V	t _{KH1} , t _{KL1}	t _{KCY1} /2 - 12	_	t _{KCY1} /2 - 21	_	t _{KCY1} /2 - 50	_	ns	
widii	2.7 V ≤ VCC ≤ 5.	.5 V		t _{KCY1} /2 - 18	_	t _{KCY1} /2 - 25	_	t _{KCY1} /2 - 50	_	ns	
	2.4 V ≤ VCC ≤ 5.	5 V	1	t _{KCY1} /2 - 38	_	t _{KCY1} /2 - 38	_	t _{KCY1} /2 - 50	_	ns	
	1.8 V ≤ VCC ≤ 5.	5 V	1	t _{KCY1} /2 - 50	_	t _{KCY1} /2 - 50	_	t _{KCY1} /2 - 50	_	ns	
	1.6 V ≤ VCC ≤ 5.	5 V		t _{KCY1} /2 - 100	_	t _{KCY1} /2 - 100	_	t _{KCY1} /2 - 100	_	ns	
SIp setup time	4.0 V ≤ VCC ≤ 5.	5 V	t _{SIK1}	44	_	54	_	110	_	ns	
(to SCKp↑)*1	2.7 V ≤ VCC ≤ 5.	5 V		44	_	54	_	110	_	ns	
	2.4 V ≤ VCC ≤ 5.	5 V		75	_	75	_	110	_	ns	
	1.8 V ≤ VCC ≤ 5.	5 V		110	_	110	_	110	_	ns	
	1.6 V ≤ VCC ≤ 5.	.5 V		220	_	220	_	220	_	ns	
SIp hold time (from SCKp↑)*1	1.6 V ≤ VCC ≤ 5.	5 V	t _{KSI1}	19	_	19	_	19	_	ns	
Delay time from SCKp↓ to SOp output*2	1.6 V ≤ VCC ≤ 5. C = 30 pF*3	5 V	t _{KSO1}	_	25	_	25	_	25	ns	

Note 1. This setting applies when SCRmn.DCP[1:0] = 00b or 11b. The setting for the SIp setup time becomes to SCKp↓ and that for the SIp hold time becomes from SCKp↓ when SCRmn.DCP[1:0] = 01b or 10b.

Note 3. C is the load capacitance of the SCKp and SOp output lines.

Note: Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR).

Note:

- p: Simplified SPI number (p = 00, 01, 10, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), gh: Port number (gh = 100 to 106, 109, 110, 112, 201, 207, 208, 212, 213, 407, 409, 915)
 - f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Note 2. This setting applies when SCRmn.DCP[1:0] = 00b or 11b. The setting for the delay time to SOp output becomes from SCKp↑ when SCRmn.DCP[1:0] = 01b or 10b.

Table 2.27 In simplified SPI communications in the slave mode with devices operating at same voltage levels with the SCKp external clock

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

				High-speed	mode	Middle-speed	mode	Low-speed me	ode		Test
Item	Conditions		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SCKp cycle	4.0 V ≤ VCC ≤ 5.5 V	20 MHz < f _{MCK}	t _{KCY2}	8/f _{MCK}	_	8/f _{MCK}	_	_	_	ns	Figure 2.17
time*4		f _{MCK} ≤ 20 MHz	1	6/f _{MCK}	_	6/f _{MCK}	_	6/f _{MCK}	_	ns	Figure 2.18
	2.7 V ≤ VCC ≤ 5.5 V	16 MHz < f _{MCK}	1	8/f _{MCK}	_	8/f _{MCK}	_	_	_	ns	1
		f _{MCK} ≤ 16 MHz]	6/f _{MCK}	_	6/f _{MCK}	_	6/f _{MCK}	_	ns	
	2.4 V ≤ VCC ≤ 5.5 V			Greater of: 6/f _{MCK} or 500	_	Greater of: 6/ f _{MCK} or 500	_	Greater of: 6/ f _{MCK} or 500	_	ns	
	1.8 V ≤ VCC ≤ 5.5 V			Greater of: 6/f _{MCK} or 750	_	Greater of: 6/ f _{MCK} or 750	_	Greater of: 6/ f _{MCK} or 750	_	ns	
SCKp high-/ low-level width	1.6 V ≤ VCC ≤ 5.5 V			Greater of: 6/f _{MCK} or 1500	_	Greater of: 6/ f _{MCK} or 1500	_	Greater of: 6/ f _{MCK} or 1500	_	ns	
	4.0 V ≤ VCC ≤ 5.5 V		t _{KH2} ,	t _{KCY2} /2 - 7	_	t _{KCY2} /2 - 7	_	t _{KCY2} /2 - 7	_	ns	
low-level width	2.7 V ≤ VCC ≤ 5.5 V		t _{KL2}	t _{KCY2} /2 - 8	_	t _{KCY2} /2 - 8	_	t _{KCY2} /2 - 8	_	ns	1
	1.8 V ≤ VCC ≤ 5.5 V		1	t _{KCY2} /2 - 18	_	t _{KCY2} /2 - 18	_	t _{KCY2} /2 - 18	_	ns	1
	1.6 V ≤ VCC ≤ 5.5 V		1	t _{KCY2} /2 - 66	_	t _{KCY2} /2 - 66	_	t _{KCY2} /2 - 66	_	ns	
SIp setup time	2.7 V ≤ VCC ≤ 5.5 V		t _{SIK2}	1/f _{MCK} + 20	_	1/f _{MCK} + 30	_	1/f _{MCK} + 30	_	ns	
(to SCKp↑)*1	1.8 V ≤ VCC ≤ 5.5 V]	1/f _{MCK} + 30	_	1/f _{MCK} + 30	_	1/f _{MCK} + 30	_	ns	
	1.6 V ≤ VCC ≤ 5.5 V			1/f _{MCK} + 40	_	1/f _{MCK} + 40	_	1/f _{MCK} + 40	_	ns	
Slp hold time (from SCKp↑)*1	1.8 V ≤ VCC ≤ 5.5 V		t _{KSI2}	1/f _{MCK} + 31	_	1/f _{MCK} + 31	_	1/f _{MCK} + 31	_	ns	
(IIOIII SCKP)	1.6 V ≤ VCC ≤ 5.5 V			1/f _{MCK} + 250	_	1/f _{MCK} + 250	_	1/f _{MCK} + 250	_	ns	
Delay time from SCKp↓ to SOp output*2	C = 30 pF ^{*3}	2.7 V ≤ VCC ≤ 5.5 V	t _{KSO2}	_	2/f _{MCK} + 44	_	2/f _{MCK} + 110	_	2/f _{MCK} + 110	ns	
output		2.4 V ≤ VCC ≤ 5.5 V		_	2/f _{MCK} + 75	_	2/f _{MCK} + 110	_	2/f _{MCK} + 110	ns	
		1.8 V ≤ VCC ≤ 5.5 V		_	2/f _{MCK} + 110	_	2/f _{MCK} + 110	_	2/f _{MCK} + 110	ns	
		1.6 V ≤ VCC ≤ 5.5 V		_	2/f _{MCK} + 220	_	2/f _{MCK} + 220	_	2/f _{MCK} + 220	ns	

Note 1. This setting applies when SCRmn.DCP[1:0] = 00b or 11b. The setting for the SIp setup time becomes to SCKp↓ and that for the SIp hold time becomes from SCKp↓ when SCRmn.DCP[1:0] = 01b or 10b.

Note: Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR).

Note:

- p: Simplified SPI number (p = 00, 01, 10, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), gh: Port number (gh = 100 to 106, 109, 110, 112, 201, 207, 208, 212, 213, 407, 409, 915)
- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Note 2. This setting applies when SCRmn.DCP[1:0] = 00b or 11b. The setting for the delay time to SOp output becomes from SCKp↑ when SCRmn.DCP[1:0] = 01b or 10b.

Note 3. C is the load capacitance of the SOp output line.

Note 4. Transfer rate in the SNOOZE mode is 1 Mbps at the maximum.

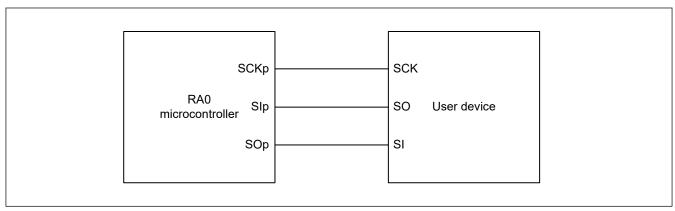


Figure 2.16 Connection in the simplified SPI communications with devices operating at same voltage levels

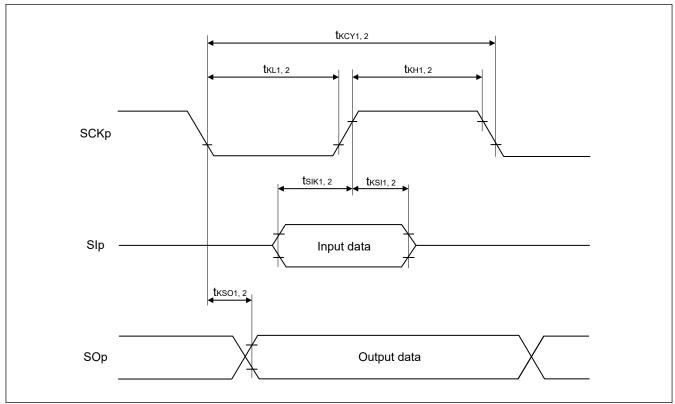


Figure 2.17 Timing of serial transfer in the simplified SPI communications with devices operating at same voltage levels when SCRmn.DCP[1:0] = 00b or 11b

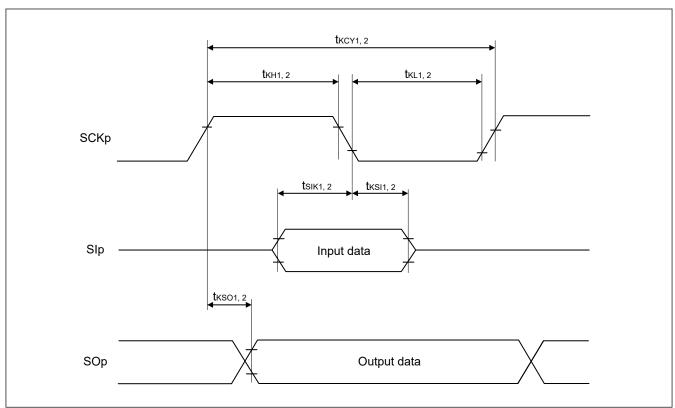


Figure 2.18 Timing of serial transfer in the simplified SPI communications with devices operating at same voltage levels when SCRmn.DCP[1:0] = 01b or 10b

Note: • p: Simplified SPI number (p = 00, 01, 10, 11, 20)

• m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Table 2.28 In simplified IIC communications with devices operating at same voltage levels (1 of 2)

			High-spee	d mode	Middle-sp	eed mode	Low-spee	d mode		Test	
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions	
SCLr clock frequency	2.7 V ≤ VCC ≤ 5.5 V, $C_b = 50 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega$	f _{SCL}	_	1000*1	_	1000*1	_	400*1	kHz	Figure 2.20	
	$1.8 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF},$ $R_b = 3 \text{ k}\Omega$		_	400*1	_	400*1	_	400*1	kHz		
	1.8 V ≤ VCC < 2.7 V, $C_b = 100 \text{ pF},$ $R_b = 5 \text{ k}\Omega$		_	300*1	_	300*1	_	300 ^{*1}	kHz		
	1.6 V ≤ VCC < 1.8 V, $C_b = 100 \text{ pF},$ $R_b = 5 \text{ k}\Omega$		_	250 ^{*1}	_	250*1	_	250 ^{*1}	kHz		
Hold time when SCLr is low	$2.7 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega$	t _{LOW}	475	_	475	_	1150	_	ns		
	$1.8 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF},$ $R_b = 3 \text{ k}\Omega$		1150	_	1150	_	1150	_	ns		
	1.8 V ≤ VCC < 2.7 V, $C_b = 100 \text{ pF},$ $R_b = 5 \text{ k}\Omega$		1550	_	1550	_	1550	_	ns		
	1.6 V ≤ VCC < 1.8 V, $C_b = 100 \text{ pF},$ $R_b = 5 \text{ k}\Omega$		1850	_	1850	_	1850	_	ns		
Hold time when SCLr is high	$2.7 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega$	tнідн	t _{HIGH}	475	_	475	_	1150	_	ns	
	$1.8 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF},$ $R_b = 3 \text{ k}\Omega$		1150	_	1150	_	1150	_	ns		
	1.8 V ≤ VCC < 2.7 V, $C_b = 100 \text{ pF},$ $R_b = 5 \text{ k}\Omega$		1550	_	1550	_	1550	_	ns		
	1.6 V ≤ VCC < 1.8 V, $C_b = 100 \text{ pF},$ $R_b = 5 \text{ k}\Omega$		1850	_	1850	_	1850	_	ns		

Table 2.28 In simplified IIC communications with devices operating at same voltage levels (2 of 2)

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

			High-speed mo	ode	Middle-speed r	node	Low-speed mo	de		Test
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
Data setup time (reception)	$2.7 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega$	t _{SU:DAT}	1/f _{MCK} + 85*2	_	1/f _{MCK} +85*2	_	1/f _{MCK} +145*2	_	ns	Figure 2.20
	1.8 V \leq VCC \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		1/f _{MCK} + 145*2	_	1/f _{MCK} + 145*2	_	1/f _{MCK} +145*2	_	ns	
	1.8 V \leq VCC $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ		1/f _{MCK} + 230*2	_	1/f _{MCK} + 230*2	_	1/f _{MCK} + 230*2	_	ns	
	1.6 V \leq VCC $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ		1/f _{MCK} + 290*2	_	1/f _{MCK} + 290*2	_	1/f _{MCK} + 290*2	_	ns	
Data hold time (transmission)	$2.7 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega$	t _{HD:DAT}	0	305	0	305	0	305	ns	
	1.8 V \leq VCC \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		0	355	0	355	0	355	ns	
	1.8 V \leq VCC $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ		0	405	0	405	0	405	ns	
	1.6 V \leq VCC $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ		0	405	0	405	0	405	ns	

Note 1. The listed times must be no greater than $f_{\mbox{\scriptsize MCK}}/4$.

Note 2. Set $f_{\mbox{\scriptsize MCK}}$ so that it will not exceed the hold time when SCLr is low or high.

Note: Select the normal input buffer and the N-ch open drain output [withstand voltage of VCC] mode for the SDAr pin and the normal output mode for the SCLr pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR).

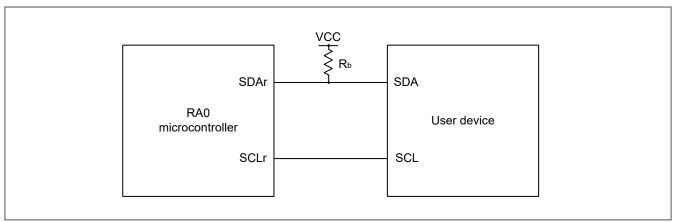


Figure 2.19 Connection in the simplified IIC communications with devices operating at same voltage levels

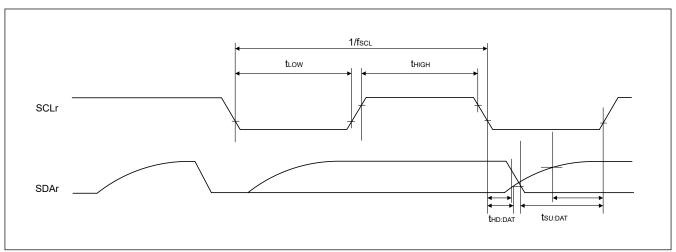


Figure 2.20 Timing of serial transfer in the simplified IIC communications with devices operating at same voltage levels

Note:

- R_b[Ω]: Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
- r: IIC number (r = 00, 01, 10, 11, 20, 21), gh: Port number (gh = 100, 102, 104, 105, 110, 112, 201, 207, 208, 212, 301, 302, 403, 409)
- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKSmn bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Table 2.29 In UART communications with devices operating at different voltage levels (1.8 V, 2.5 V, 3 V) (1)

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

					High-s	peed mode	Middle-s	peed mode	Low-sp	eed mode		Test
Para	amet	er		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
Transfer rate	Reception	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$		_	_	f _{MCK} /6*1	_	f _{MCK} /6*1	_	f _{MCK} /6*1	bps	Figure 2.22
Tra	<u> </u>		Theoretical value of the maximum transfer rate f_{MCK} = PCLKB*3		_	5.3	_	4	_	0.33	Mbps	
		$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$			_	f _{MCK} /6*1	_	f _{MCK} /6*1	_	f _{MCK} /6*1	bps	
			Theoretical value of the maximum transfer rate $f_{MCK^{*3}} = PCLKB^{*3}$		_	5.3	_	4	_	0.33	Mbps	
		1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			_	f _{MCK} /6*1 *2	_	f _{MCK} /6*1 *2	_	f _{MCK} /6*1 *2	bps	
			Theoretical value of the maximum transfer rate $f_{MCK} = PCLKB^{*3}$		_	5.3	_	4	_	0.33	Mbps	

- Note 1. Transfer rate in the SNOOZE mode is within the range from 4800 to 9600 bps.
- Note 2. Use this rate with VCC $\geq V_b$.
- Note 3. The maximum operating frequencies of the system clock (PCLKB) are: High-speed mode: 32 MHz (1.8 V \leq VCC \leq 5.5 V), 4 MHz (1.6 V \leq VCC \leq 5.5 V) Middle-speed mode: 24 MHz (1.8 V \leq VCC \leq 5.5 V), 4 MHz (1.6 V \leq VCC \leq 5.5 V) Low-speed mode: 2 MHz (1.6 V \leq VCC \leq 5.5 V)

Note: Select the TTL input buffer for the RXDq pin and the N-ch open drain output [withstand voltage of VCC] mode for the TXDq pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Note: • V_b[V]: Communication line voltage

• q: UART number (q = 0 to 2), gh: Port number (gh = 100, 101, 109, 110, 212, 213)

f_{MCK}: Serial array unit operation clock frequency To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

In UART communications with devices operating at different voltage levels (1.8 V, 2.5 V, 3 V) **Table 2.30**

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

					High-sp	eed mode	Middle-sp	eed mode	Low-spe	eed mode		Test
Par	amet	ter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
Transfer rate	Transmission	4.0 V ≤ VCC ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		_	_	*1	_	*1	_	*1	bps	Figure 2.22
Trai	Trar		Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF},$ $R_b = 1.4 \text{ k}\Omega,$ $V_b = 2.7 \text{ V}$		_	2.8*2	_	2.8*2	_	2.8*2	Mbps	
		2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V			_	*3	_	*3	_	*3	bps	
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega,$ $V_b = 2.3 \text{ V}$		_	1.2*4	_	1.2*4	_	1.2*4	Mbps	
		1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V	l		_	*5 *6	_	*5 *6	_	*5 *6	bps	
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF},$ $R_b = 5.5 \text{ k}\Omega,$ $V_b = 1.6 \text{ V}$		_	0.43*7	_	0.43*7	_	0.43*7	Mbps	

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 4.0 V \leq VCC \leq 5.5 V, 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\left\{-C_b \times R_b \times \ln\left(1 - \frac{2.2}{V_b}\right)\right\} \times 3} [bps]$$
Baud rate error (theoretical value) =
$$\frac{1}{\frac{1}{\text{Transfer rate}} \times 2} - \left\{-C_b \times R_b \times \ln\left(1 - \frac{2.2}{V_b}\right)\right\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100[\%]$$
This value is the theoretical value of the relative difference between the transmission and recent

This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 2. This rate is calculated as an example when the conditions described in the Conditions column are met. See *1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 2.7 V \leq VCC < 4.0 V, 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\left\{-C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right)\right\} \times 3} [bps]$$
Baud rate error (theoretical value) =
$$\frac{1}{\frac{1}{\text{Transfer rate} \times 2} - \left\{-C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right)\right\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100[\%]$$

This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 4. This rate is calculated as an example when the conditions described in the Conditions column are met. See *3 above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use this rate with VCC $\geq V_b$.

Note 6. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 1.8 V \leq VCC < 3.3 V, 1.6 V \leq V $_b$ \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\left\{-C_b \times R_b \times \ln\left(1 - \frac{1.5}{V_b}\right)\right\} \times 3} [bps]$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \left\{ -C_b \times R_b \times \ln\left(1 - \frac{1.5}{V_b}\right) \right\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 [\%]$$

This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 7. This rate is calculated as an example when the conditions described in the Conditions column are met. See *6 above to calculate the maximum transfer rate under conditions of the customer.

Note: Select the TTL input buffer for the RXDq pin and the N-ch open drain output [withstand voltage of VCC] mode for the TXDq pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{II}, see the DC characteristics with TTL input buffer selected.

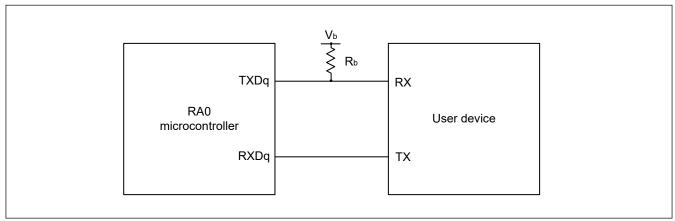


Figure 2.21 In UART communications with devices operating at different voltage levels

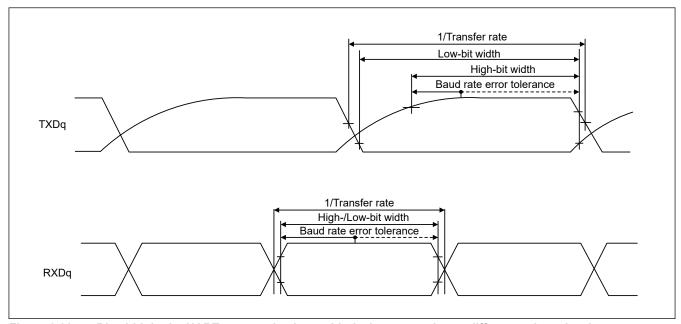


Figure 2.22 Bit width in the UART communications with devices operating at different voltage levels (reference)

Note: • $R_b[\Omega]$: Communication line (TXDq) pull-up resistance, $C_b[F]$: Communication line (TXDq) load capacitance, $V_b[V]$: Communication line voltage

- q: UART number (q = 0 to 2), gh: Port number (gh = 100, 101, 109, 110, 212, 213)
- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)
- Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

Table 2.31 In simplified SPI communications in the master mode with devices operating at different voltage levels (2.5 V or 3 V) with the internal SCKp clock (the ratings below are only applicable to SPI00)

Conditions: VCC = 2.7 to 5.5 V. VSS = 0 V. Ta = -40 to +105°C

				High-speed	mode	Middle-spe mode	ed	Low-speed	mode		Test
Parameter			Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SCKp cycle time	t _{KCY1} ≥ 2/PCLKB	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 20 \text{ pF},$ $R_b = 1.4 \text{ kΩ}$	t _{KCY1}	200	_	200	_	2300	_	ns	Figure 2.24 Figure 2.25
		$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 20 \text{ pF},$ $R_b = 2.7 \text{ k}\Omega$		300	_	300	_	2300	_	ns	
SCKp high-level width	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF, } R_b = 1.4 \text{ k}\Omega$	t _{KH1}	t _{KCY1} /2 - 50	_	t _{KCY1} /2 - 50	_	t _{KCY1} /2 - 50	_	ns	
widti	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}, \text{ C}$	$C_{b} = 20 \text{ pF, } R_{b} = 2.7 \text{ k}\Omega$		t _{KCY1} /2 - 120		t _{KCY1} /2 - 120	_	t _{KCY1} /2 - 120	_	ns	
SCKp low-level width	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF, } R_b = 1.4 \text{ k}\Omega$	t _{KL1}	t _{KCY1} /2 -7		t _{KCY1} /2 -7	_	t _{KCY1} /2 - 50	-	ns	
widtii	2.7 V ≤ VCC < 4.0 V 2.3 V ≤ V _b ≤ 2.7 V, C	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		t _{KCY1} /2 - 10	_	t _{KCY1} /2 - 10	_	t _{KCY1} /2 - 50	_	ns	
SIp setup time (to	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	t _{SIK1}	58	_	58	_	479	_	ns	
SCKp↑)*1	2.7 V ≤ VCC < 4.0 V 2.3 V ≤ V _b ≤ 2.7 V, C	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		121	_	121	_	479	_	ns	
Slp hold time (from	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	t _{KSI1}	10	_	10	_	10	_	ns	
SCKp↑)*1	2.7 V ≤ VCC < 4.0 V 2.3 V ≤ V _b ≤ 2.7 V, C	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		10	_	10	_	10	_	ns	
Delay time from	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	t _{KSO1}	_	60	_	60	_	60	ns	
SCKp↓ to SOp output*1	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}, \text{ C}$	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		_	130	_	130	_	130	ns	
SIp setup	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}, \text{ C}$	$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	t _{SIK1}	23	-	23	_	110	-	ns	
(to SCKp↓) ^{*2}	2.7 V ≤ VCC < 4.0 V 2.3 V ≤ V _b ≤ 2.7 V, C	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		33	_	33		110	-	ns	
SIp hold time	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	t _{KSI1}	10	_	10		10	_	ns	
(from SCKp↓) ^{*2}	2.7 V ≤ VCC < 4.0 V 2.3 V ≤ V _b ≤ 2.7 V, C	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		10	_	10	_	10	-	ns	
Delay time from	4.0 V ≤ VCC ≤ 5.5 V 2.7 V ≤ V _b ≤ 4.0 V, C	$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	t _{KSO1}	_	10	_	10	_	10	ns	
SCKp↑ to SOp output*2	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V}$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}, \text{ C}$	$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		_	10	_	10	_	10	ns	

Note 1. This setting applies when SCRmn.DCP[1:0] = 00b or 11b.

Note 2. This setting applies when SCRmn.DCP[1:0] = 01b or 10b.

Note: Select the TTL input buffer for the SIp pin and the N-ch open drain output [withstand voltage of VCC] mode for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Note:

- $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
- p: Simplified SPI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), gh: Port number (gh = 100 to 103, 112, 201)
- f_{MCK}: Serial array unit operation clock frequency

To set this operating clock, use the CKSmn bit in the serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)

Table 2.32 In simplified SPI communications in the master mode with devices operating at different voltage levels (1.8 V, 2.5 V, or 3 V) with the internal SCKp clock (1)

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

				High-speed	mode	Middle-speed	l mode	Low-speed	mode		Test
Parameter			Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SCKp cycle time	t _{KCY1} ≥ 4/ PCLKB	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF},$ $R_b = 1.4 \text{ kΩ}$	t _{KCY1}	300	_	300	_	2300	_	ns	Figure 2.24 Figure 2.25
				500	_	500	_	2300	_	ns	
		1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V*1, C _b = 30 pF, R _b = 5.5 k Ω		1150	_	1150	_	2300	_	ns	
SCKp high- level width	$4.0 \text{ V} \le \text{VCC} \le \frac{1}{2.7} \text{ V} \le \text{V}_b \le 4.0 \text{ C}_b = 30 \text{ pF, R}_b$	V,	t _{KH1}	t _{KCY1} /2 - 75	_	t _{KCY1} /2 - 75	_	t _{KCY1} /2 - 75	_	ns	
	$2.7 \text{ V} \leq \text{VCC} < 4$ $2.3 \text{ V} \leq \text{V}_b \leq 2.7$ $C_b = 30 \text{ pF}, R_b$	' V,		t _{KCY1} /2 - 170	_	t _{KCY1} /2 - 170	_	t _{KCY1} /2 - 170	_	ns	
	1.8 V \leq VCC < 3 1.6 V \leq V _b \leq 2.0 C _b = 30 pF, R _b) V*1,		t _{KCY1} /2 - 458	_	t _{KCY1} /2 - 458	_	t _{KCY1} /2 - 458	_	ns	
SCKp low- level width	$4.0 \text{ V} \le \text{VCC} \le \frac{1}{2.7} \text{ V} \le \text{V}_b \le 4.0 \text{ C}_b = 30 \text{ pF, R}_b$) V,	t _{KL1}	t _{KCY1} /2 -12	_	t _{KCY1} /2 -12	_	t _{KCY1} /2 - 50	_	ns	
	$2.7 \text{ V} \leq \text{VCC} < 4$ $2.3 \text{ V} \leq \text{V}_b \leq 2.7$ $C_b = 30 \text{ pF}, R_b = 4$	' V,		t _{KCY1} /2 - 18	_	t _{KCY1} /2 - 18	_	t _{KCY1} /2 - 50	_	ns	
	1.8 V \leq VCC < 3 1.6 V \leq V _b \leq 2.0 C _b = 30 pF, R _b) V*1,		t _{KCY1} /2 - 50	_	t _{KCY1} /2 - 50	_	t _{KCY1} /2 - 50		ns	

Note 1. Use this setting with VCC $\geq V_b$.

Note: Select the TTL input buffer for the SIp pin and the N-ch open drain output [withstand voltage of VCC] mode for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Table 2.33 In simplified SPI communications in the master mode with devices operating at different voltage levels (1.8 V, 2.5 V, or 3 V) with the internal SCKp clock (2)

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

			High-sp	eed mode	Middle-s	speed mode	Low-sp	eed mode		Test
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SIp setup time (to SCKp↑)*1		t _{SIK1}	81	_	81	_	479	_	ns	Figure 2.24 Figure 2.25
	2.7 V \leq VCC $<$ 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 30 pF, R _b = 2.7 k Ω		177	_	177	_	479	_	ns	
	1.8 $V \le VCC < 3.3 V$, 1.6 $V \le V_b \le 2.0 V^{*2}$, $C_b = 30 pF$, $R_b = 5.5 k\Omega$		479	_	479	_	479	_	ns	
SIp hold time (from SCKp↑)*1	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}Ω$	t _{KSI1}	19	_	19	_	19	_	ns	
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		19	_	19	_	19	_	ns	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V^{*2} , C_b = 30 pF, R_b = 5.5 kΩ		19	_	19	_	19	_	ns	
Delay time from SCKp↓ to SOp output*1	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}Ω$	t _{KSO1}	_	100	_	100	_	100	ns	
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		_	195	_	195	_	195	ns	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V^{*2} , C_b = 30 pF, R_b = 5.5 kΩ		_	483	_	483	_	483	ns	

Note 1. This setting applies when SCRmn.DCP[1:0] = 00b or 11b.

Note: Select the TTL input buffer for the SIp pin and the N-ch open drain output [withstand voltage of VCC] mode for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Note 2. Use this setting with $VCC \ge V_b$.

Table 2.34 In simplified SPI communications in the master mode with devices operating at different voltage levels (1.8 V, 2.5 V, or 3 V) with the internal SCKp clock (3)

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

			High-s	peed mode	Middle-	speed mode	Low-speed mode			Test
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Conditions
SIp setup time (to SCKp↓)*1	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF},$ $R_b = 1.4 \text{ k}Ω$	t _{SIK1}	44	_	44		110	_	ns	Figure 2.24 Figure 2.25
	2.7 V \leq VCC $<$ 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 30 pF, R _b = 2.7 k Ω		44	_	44	_	110	_	ns	
	1.8 $V \le VCC < 3.3 V$, 1.6 $V \le V_b \le 2.0 V^{*2}$, $C_b = 30 pF$, $R_b = 5.5 k\Omega$		110	_	110		110	_	ns	
SIp hold time (from SCKp↓)*1	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}Ω$	t _{KSI1}	19	_	19	_	19	_	ns	
	2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		19	_	19	_	19	_	ns	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V^{*2} , C_b = 30 pF, R_b = 5.5 kΩ		19	_	19	_	19	_	ns	
Delay time from SCKp↑ to SOp output*1	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}Ω$	t _{KSO1}	_	25	_	25	_	25	ns	
	2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		_	25	_	25	_	25	ns	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V* ² , C _b = 30 pF, R _b = 5.5 kΩ		_	25	_	25	_	25	ns	

Note 1. This setting applies when SCRmn.DCP[1:0] = 01b or 10b.

Note 2. Use this setting with VCC $\geq V_b$.

Note: Select the TTL input buffer for the SIp pin and the N-ch open drain output [withstand voltage of VCC] mode for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

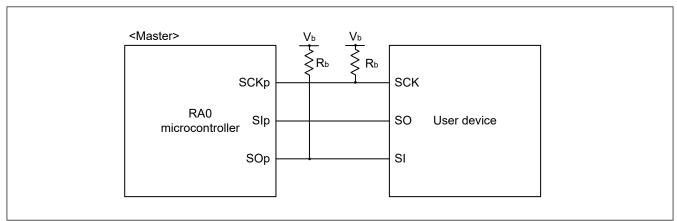


Figure 2.23 Connection in the simplified SPI communications with devices operating at different voltage levels

Note: • R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

• p: Simplified SPI number (p = 00, 01, 10, 11, 20), m: Unit number, n: Channel number (mn = 00 to 03, 10, 11), gh: Port number (gh = 100 to 106, 109, 110, 112, 201, 207, 208, 212, 213, 407, 409, 915)

- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)
- Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

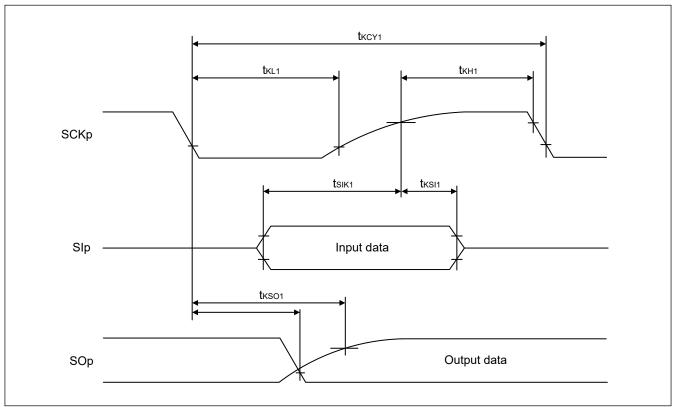


Figure 2.24 Timing of serial transfer in the simplified SPI communications in the master mode with devices operating at different voltage levels when SCRmn.DCP[1:0] = 00b or 11b

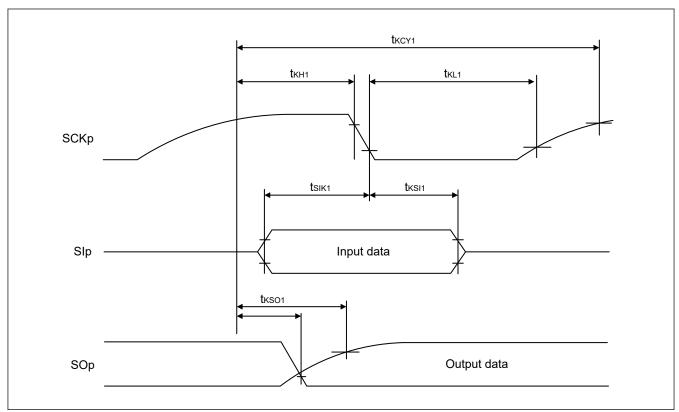


Figure 2.25 Timing of serial transfer in the simplified SPI communications in the master mode with devices operating at different voltage levels when SCRmn.DCP[1:0] = 01b or 10b

Note:

- p: Simplified SPI number (p = 00, 01, 10, 11, 20), m: Unit number, n: Channel number (mn = 00 to 03, 10, 11), gh: Port number (gh = 100 to 106, 109, 110, 112, 201, 207, 208, 212, 213, 407, 409, 915)
- Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS A and P213PFS A registers do not have PIM bit.

Table 2.35 In simplified SPI communications in the slave mode with devices operating at different voltage levels (1.8 V, 2.5 V, or 3 V) with the external SCKp clock

	CC = 1.8 to 5.5 V, VSS =			High-spee	d mode	Middle-spe	ed mode	Low-speed	l mode		T4
Parameter			Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Test Conditions
SCKp cycle	4.0 V ≤ VCC ≤ 5.5 V,	24 MHz < f _{MCK}	t _{KCY2}	14/f _{MCK}	_	_	_	Ī-	-	ns	Figure 2.27
time*1	$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	20 MHz < f _{MCK} ≤ 24 MHz		12/f _{MCK}	_	12/f _{MCK}	_	_	_	ns	Figure 2.28
		8 MHz < f _{MCK} ≤ 20 MHz	-	10/f _{MCK}	_	10/f _{MCK}	_	_	_	ns	
		4 MHz < f _{MCK} ≤ 8 MHz	1	8/f _{MCK}	1-	8/f _{MCK}	<u> </u>	-	-	ns	
		f _{MCK} ≤ 4 MHz	1	6/f _{MCK}	-	6/f _{MCK}	<u> </u>	10/f _{MCK}	_	ns	
	2.7 V ≤ VCC < 4.0 V,	24 MHz < f _{MCK}	1	20/f _{MCK}	_	_	_	_	_	ns	
	$2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	20 MHz < f _{MCK} ≤ 24 MHz]	16/f _{MCK}	_	16/f _{MCK}	_	_	_	ns	
		16 MHz < f _{MCK} ≤ 20 MHz	1	14/f _{MCK}	-	14/f _{MCK}	<u> </u>	-	_	ns	
		8 MHz < f _{MCK} ≤ 16 MHz]	12/f _{MCK}	_	12/f _{MCK}	_	_	_	ns	
		4 MHz < f _{MCK} ≤ 8 MHz]	8/f _{MCK}	_	8/f _{MCK}	_	_	_	ns	
		f _{MCK} ≤ 4 MHz]	6/f _{MCK}	_	6/f _{MCK}	_	10/f _{MCK}	_	ns	
	1.8 V ≤ VCC < 3.3 V,	24 MHz < f _{MCK}]	48/f _{MCK}	_	_	_	_	_	ns	
	$1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{*2}$	20 MHz < f _{MCK} ≤ 24 MHz]	36/f _{MCK}	_	36/f _{MCK}	_	_	_	ns	
		16 MHz < f _{MCK} ≤ 20 MHz]	32/f _{MCK}	_	32/f _{MCK}	_	_	_	ns	
		8 MHz < f _{MCK} ≤ 16 MHz		26/f _{MCK}	_	26/f _{MCK}	_	_	_	ns	
		4 MHz < f _{MCK} ≤ 8 MHz		16/f _{MCK}	_	16/f _{MCK}	_	_	_	ns	
		f _{MCK} ≤ 4 MHz		10/f _{MCK}	_	10/f _{MCK}	_	10/f _{MCK}	-	ns	
SCKp high-/ low-level width	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$		t _{KH2} , t _{KL2}	t _{KCY2} /2 - 12	_	t _{KCY2} /2 - 12	_	t _{KCY2} /2 - 50	_	ns	
widti	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$			t _{KCY2} /2 - 18	_	t _{KCY2} /2 - 18	_	t _{KCY2} /2 - 50	_	ns	
	1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{*2}			t _{KCY2} /2 - 50	_	t _{KCY2} /2 - 50	_	t _{KCY2} /2 - 50	_	ns	
SIp setup time	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$		t _{SIK2}	1/f _{MCK} + 20	_	1/f _{MCK} + 20	_	1/f _{MCK} + 30	_	ns	
(to SCKp↑)*3	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$			1/f _{MCK} + 20	_	1/f _{MCK} + 20	_	1/f _{MCK} + 30	_	ns	
	1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{*2}			1/f _{MCK} + 30	_	1/f _{MCK} + 30	_	1/f _{MCK} + 30	_	ns	
SIp hold time (from SCKp↑)*3			t _{KSI2}	1/f _{MCK} + 31	_	1/f _{MCK} + 31	_	1/f _{MCK} + 31	_	ns	
Delay time from SCKp↓ to SOp output*4	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}$	Ω	t _{KSO2}	_	2/f _{MCK} + 120		2/f _{MCK} + 120	_	2/f _{MCK} + 573	ns	
output .	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}$	Ω		_	2/f _{MCK} + 214		2/f _{MCK} + 214		2/f _{MCK} + 573	ns	
	1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V ² , C _b = 30 pF, R _b = 5.5 k	Ω		_	2/f _{MCK} + 573	_	2/f _{MCK} + 573	_	2/f _{MCK} + 573	ns	

Note 1. Transfer rate in the SNOOZE mode: 1 Mbps (max.) Note 2. Use this setting with VCC \geq V_b.

Select the TTL input buffer for the SIp pin and the N-ch open drain output [withstand voltage of VCC] mode Note: for the SOp pin and SCKp pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Note 3. This setting applies when SCRmn.DCP[1:0] = 00b or 11b. The SIp setup time becomes to SCKp↓ and SIp hold time becomes from SCKp↓ when SCRmn.DCP[1:0] = 01b or 10b.

Note 4. This setting applies when SCRmn.DCP[1:0] = 00b or 11b. The delay time to SOp output becomes from SCKp↑ when SCRmn.DCP[1:0] = 01b or 10b.

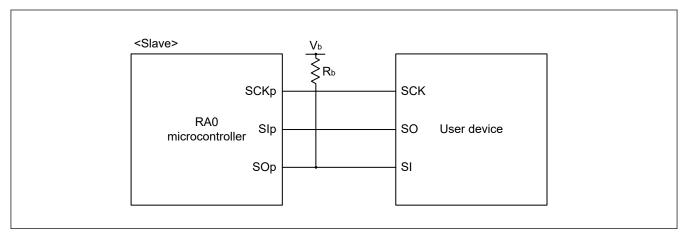


Figure 2.26 Connection in the simplified SPI communications with devices operating at different voltage levels

Note:

- R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]:
 Communication line voltage
- p: Simplified SPI number (p = 00, 01, 10, 11, 20), m: Unit number, n: Channel number (mn = 00 to 03, 10, 11), gh: Port number (gh = 100 to 106, 109, 110, 112, 201, 207, 208, 212, 213, 407, 409, 915)
- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)
- Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

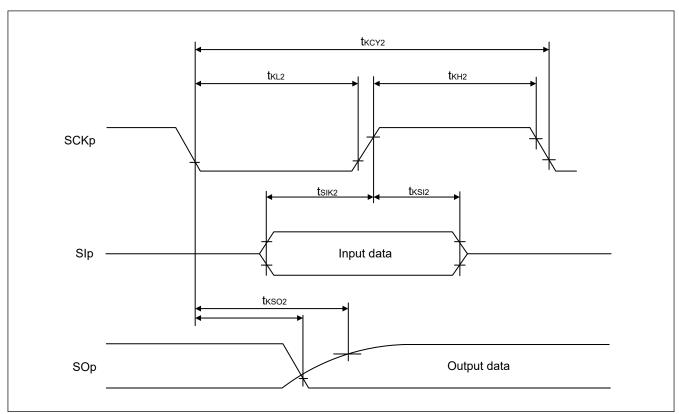


Figure 2.27 Timing of serial transfer in the simplified SPI communications in the slave mode with devices operating at different voltage levels when SCRmn.DCP[1:0] = 00b or 11b

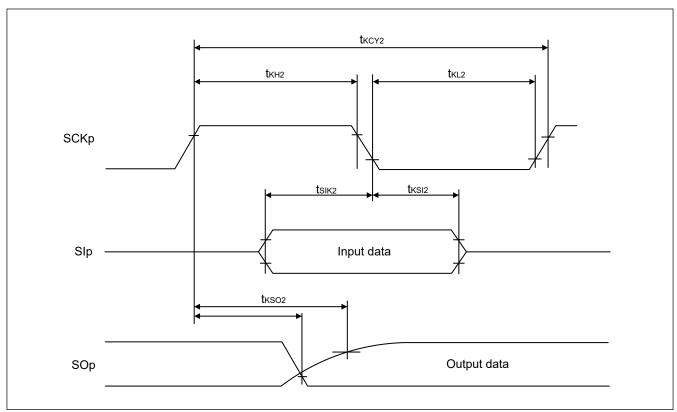


Figure 2.28 Timing of serial transfer in the simplified SPI communications in the slave mode with devices operating at different voltage levels when SCRmn.DCP[1:0] = 01b or 10b

Note:

- p: Simplified SPI number (p = 00, 01, 10, 11, 20), m: Unit number, n: Channel number (mn = 00 to 03, 10, 11), gh: Port number (gh = 100 to 106, 109, 110, 112, 201, 207, 208, 212, 213, 407, 409, 915)
- Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS A and P213PFS A registers do not have PIM bit.

Table 2.36 Simplified IIC communications with devices operating at different voltage levels (1.8 V, 2.5 V, or 3 V) (1 of 2)

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

			High-speed	mode	Middle-spee	ed mode	Low-speed mode			
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Test Conditions
SCLr clock frequency	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}Ω$	f _{SCL}	_	1000*1	_	1000*1	_	300*1	kHz	Figure 2.30
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}Ω$		_	1000 ^{*1}	_	1000*1	_	300*1	kHz	
	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}Ω$		_	400*1	_	400*1	_	300*1	kHz	
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		_	400 ^{*1}	_	400*1	_	300 ^{*1}	kHz	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V^{*2} , C_b = 100 pF, R_b = 5.5 kΩ		_	300 ^{*1}	_	300*1	_	300*1	kHz	
Hold time when SCLr is low	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}Ω$	t _{LOW}	475	_	475	_	1550	-	ns	
	2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		475	_	475	-	1550	_	ns	
	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}Ω$		1150	_	1550	-	1550	_	ns	
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		1150	_	1550	-	1550	_	ns	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V^{*2} , C_b = 100 pF, R_b = 5.5 kΩ		1550	_	1550	-	1550	-	ns	
Hold time when SCLr is high	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}Ω$	thigh	245	-	245	_	610	-	ns	
	2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		200	_	200	_	610	-	ns	
	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}Ω$		675	_	675	_	610	-	ns	
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		600	-	600	-	610	-	ns	
	1.8 V ≤ VCC < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V^{*2} , C_b = 100 pF, R_b = 5.5 kΩ		610	_	610	-	610	-	ns	

Table 2.36 Simplified IIC communications with devices operating at different voltage levels (1.8 V, 2.5 V, or 3 V) (2 of 2)

Conditions: VCC = 1.8 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

			High-speed mod	le	Middle-speed m	ode	Low-speed mode	•		
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Test Conditions
Data setup time (reception)	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ kΩ}$	t _{SU:DAT}	1/f _{MCK} +135*3	-	1/f _{MCK} +135*3	-	1/f _{MCK} +190*3	_	ns	Figure 2.30
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		1/f _{MCK} +135 ^{*3}	-	1/f _{MCK} +135 ^{*3}	-	1/f _{MCK} +190 ^{*3}	_	ns	
	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}Ω$		1/f _{MCK} +190*3	-	1/f _{MCK} +190*3	-	1/f _{MCK} +190*3	_	ns	
	2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		1/f _{MCK} +190 ^{*3}	-	1/f _{MCK} +190 ^{*3}	-	1/f _{MCK} +190 ^{*3}	_	ns	
	1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V*2, C _b = 100 pF, R _b = 5.5 k Ω		1/f _{MCK} +190 ^{*3}	_	1/f _{MCK} +190*3	_	1/f _{MCK} +190*3	_	ns	
Data hold time (transmission)	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}Ω$	t _{HD:DAT}	0	305	0	305	0	305	ns	
	$2.7 \text{ V} \le \text{VCC} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		0	305	0	305	0	305	ns	
	$4.0 \text{ V} \le \text{VCC} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}Ω$		0	355	0	355	0	355	ns	
	2.7 V ≤ VCC < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		0	355	0	355	0	355	ns	
	1.8 V \leq VCC $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V*2, C _b = 100 pF, R _b = 5.5 k Ω		0	405	0	405	0	405	ns	

- Note 1. The listed times must be no greater than $f_{MCK}/4$.
- Note 2. Use this setting with VCC $\geq V_b$.
- Note 3. Set f_{MCK} so that it will not exceed the hold time when SCLr is low or high.

Note: Select the TTL input buffer and the N-ch open drain output [withstand voltage of VCC] mode for the SDAr pin and the N-ch open drain output [withstand voltage of VCC] mode for the SCLr pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

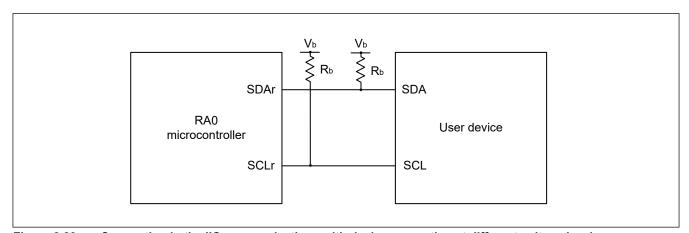


Figure 2.29 Connection in the IIC communications with devices operating at different voltage levels

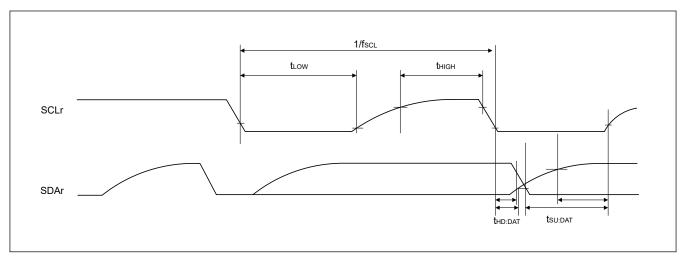


Figure 2.30 Timing of serial transfer in the simplified IIC communications with devices operating at different voltage levels

- r: Simplified IIC number (r = 00, 01, 10, 11, 20, 21), gh: Port number (gh = 100, 102, 104, 105, 110, 112, 201, 207, 208, 212, 301, 302, 403, 409)
- f_{MCK}: Serial array unit operation clock frequency
 To set this operating clock, use the CKS bit in the serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

2.5.2 UART Interface (UARTA)

Table 2.37 UARTA communications

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Transfer rate	_	200	0	153600	bps	_

Note: Select the normal input buffer for the RXDAn pin and the normal output mode for the TXDAn pin by using the Port gh Pin Function Select Register (PghPFS_A.PIM and PghPFS_A.NCODR).

Note: n: Unit number (n = 0, 1), gh: Port number (gh = 100 to 103, 105, 106, 109, 110, 207, 208, 212, 213, 301, 302)

Note: Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

2.5.3 I²C Bus Interface (IICA)

Table 2.38 |2C standard mode

Conditions: VCC = 1.6 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
SCLAn clock frequency	Standard mode: PCLKB ≥ 1 MHz	f _{SCL}	0	_	100	kHz	Figure 2.31
Setup time of restart condition	_	t _{SU:STA}	4.7	_	_	μs	
Hold time*1	_	t _{HD:STA}	4	_	_	μs	
Hold time when SCLAn is low	_	t _{LOW}	4.7	_	_	μs	
Hold time when SCLAn is high	_	t _{HIGH}	4	_	_	μs	
Data setup time (reception)	_	t _{SU:DAT}	250	_	_	ns	
Data hold time (transmission)*2	_	t _{HD:DAT}	0	_	3.45	μs	
Setup time of stop condition	_	t _{SU:STO}	4	_	_	μs	
Bus-free time	_	t _{BUF}	4.7	_	_	μs	

Note 1. The first clock pulse is generated after this period when the start or restart condition is detected.

Note 2. The maximum value of t_{HD:DAT} applies to normal transfer. The clock stretching will be inserted on reception of an acknowledgment (ACK) signal.

Note: n: Unit number (0,1)

Note: Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

Note: The maximum value of communication line capacitance (C_b) and communication line pull-up resistor (R_b) are as

 $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

Table 2.39 I²C fast mode

Conditions: VCC = 1.8 to 5.5 V. VSS = 0 V. Ta = -40 to +125°C

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
SCLAn clock frequency	Fast mode: PCLKB ≥ 3.5 MHz 1.8 V ≤ VCC ≤ 5.5 V	f _{SCL}	0	_	400	kHz	Figure 2.31
Setup time of restart condition	1.8 V ≤ VCC ≤ 5.5 V	t _{SU:STA}	0.6	_	_	μs	
Hold time*1	1.8 V ≤ VCC ≤ 5.5 V	t _{HD:STA}	0.6	_	_	μs	
Hold time when SCLAn is low	1.8 V ≤ VCC ≤ 5.5 V	t _{LOW}	1.3	_	_	μs	
Hold time when SCLAn is high	1.8 V ≤ VCC ≤ 5.5 V	t _{HIGH}	0.6	_	_	μs	
Data setup time (reception)	1.8 V ≤ VCC ≤ 5.5 V	t _{SU:DAT}	100	_	_	ns	
Data hold time (transmission)*2	1.8 V ≤ VCC ≤ 5.5 V	t _{HD:DAT}	0	_	0.9	μs	
Setup time of stop condition	1.8 V ≤ VCC ≤ 5.5 V	t _{SU:STO}	0.6	_	_	μs	
Bus-free time	1.8 V ≤ VCC ≤ 5.5 V	t _{BUF}	1.3	_	_	μs	

Note 1. The first clock pulse is generated after this period when the start or restart condition is detected.

Note 2. The maximum value of t_{HD:DAT} applies to normal transfer. The clock stretching will be inserted on reception of an acknowledgment (ACK) signal.

Note: Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS_A and P213PFS_A registers do not have PIM bit.

Note: The maximum value of communication line capacitance (C_b) and communication line pull-up resistor (R_b) are as follows.

 $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

Table 2.40 I²C fast mode plus

Conditions: VCC = 2.7 to 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
SCLAn clock frequency	Fast mode plus: PCLKB ≥ 10 MHz 2.7 V ≤ VCC ≤ 5.5 V	f _{SCL}	0	_	1000	kHz	Figure 2.31
Setup time of restart condition	2.7 V ≤ VCC ≤ 5.5 V	t _{SU:STA}	0.26	_	_	μs	
Hold time*1	2.7 V ≤ VCC ≤ 5.5 V	t _{HD:STA}	0.26	_	_	μs	
Hold time when SCLAn is low	2.7 V ≤ VCC ≤ 5.5 V	t _{LOW}	0.5	_	_	μs	
Hold time when SCLAn is high	2.7 V ≤ VCC ≤ 5.5 V	t _{HIGH}	0.26	_	_	μs	
Data setup time (reception)	2.7 V ≤ VCC ≤ 5.5 V	t _{SU:DAT}	50	_	_	ns	
Data hold time (transmission)*2	2.7 V ≤ VCC ≤ 5.5 V	t _{HD:DAT}	0	_	0.45	μs	
Setup time of stop condition	2.7 V ≤ VCC ≤ 5.5 V	t _{SU:STO}	0.26	_	_	μs	
Bus-free time	2.7 V ≤ VCC ≤ 5.5 V	t _{BUF}	0.5	_	_	μs	

Note 1. The first clock pulse is generated after this period when the start or restart condition is detected.

Note 2. The maximum value of t_{HD:DAT} applies to normal transfer. The clock stretching will be inserted on reception of an acknowledgment (ACK) signal.

Note: Communications by using P212 and P213 with devices operating at different voltage levels are not possible since P212PFS A and P213PFS A registers do not have PIM bit.

Note: The maximum value of communication line capacitance (C_b) and communication line pull-up resistor (R_b) are as follows.

 $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

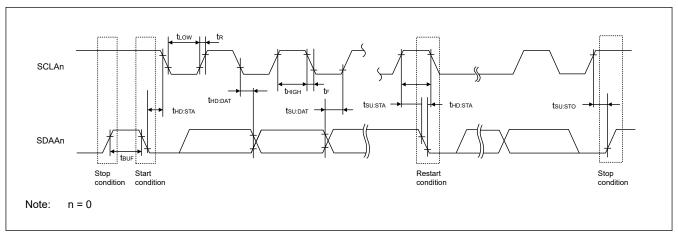


Figure 2.31 IICA serial transfer timing

2.6 Analog Characteristics

2.6.1 A/D Converter Characteristics

Table 2.41 A/D conversion characteristics in Normal modes 1 and 2 (1 of 2)

Conditions: $2.4V \le VREFH0 \le VCC \le 5.5 V$, VSS = 0 V, Ta = -40 to +125°C

Reference voltage range applied to the VREFH0 (ADVREFP[1:0] = 01b) and VREFL0 (ADVREFM = 1b).

Target pins: AN000 to AN012, AN021 to AN022, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Resolution	RES	8	_	12	bit	_
Conversion clock	f _{AD}	1	_	32	MHz	_

Table 2.41 A/D conversion characteristics in Normal modes 1 and 2 (2 of 2)

Conditions: $2.4V \le VREFH0 \le VCC \le 5.5 \text{ V, VSS} = 0 \text{ V, Ta} = -40 \text{ to } +125^{\circ}\text{C}$

Reference voltage range applied to the VREFH0 (ADVREFP[1:0] = 01b) and VREFL0 (ADVREFM = 1b).

Target pins: AN000 to AN012, AN021 to AN022, internal reference voltage, and temperature sensor output voltage

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions	
Overall error*1 *3 *4 *5	12-bit	AINL	_	_	±7.5	LSB	4.5 V ≤ VREFH0 = VCC ≤ 5.5 V	
	resolution		_	_	±9.0	LSB	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V	
			_	_	±9.0	LSB	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V	
Conversion time*6	12-bit	t _{CONV}	2.0	_	_	μs	4.5 V ≤ VREFH0 = VCC ≤ 5.5 V	
	resolution		2.0	_	_	μs	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V	
			2.0	_	_	μs	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V	
Zero-scale error*1 *2 *3 *4 *5	12-bit resolution	E _{ZS}	_	_	±0.17	%FSR	4.5 V ≤ VREFH0 = VCC ≤ 5.5 V	
		resolution	resolution		_	_	±0.21	%FSR
			_	_	±0.21	%FSR	2.4 V ≤ VREFH 0 =VCC ≤ 5.5 V	
Full-scale error*1 *2 *3 *4 *5	12-bit	on E _{FS}	_	_	±0.17	%FSR	4.5 V ≤ VREFH0 = VCC ≤ 5.5 V	
	resolution		_	_	±0.21	%FSR	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V	
			_	_	±0.21	%FSR	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V	
Integral linearity error*1 *4 *5	12-bit	ILE	_	_	±3.0	LSB	4.5 V ≤ VREFH0 = VCC ≤ 5.5 V	
	resolution		_	_	±3.0	LSB	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V	
			_	_	±3.0	LSB	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V	
Differential linearity error*1	12-bit	DLE	_	±1.0	_	LSB	4.5 V ≤ VREFH0 = VCC ≤ 5.5 V	
	resolution		_	±1.0	_	LSB	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V	
			_	±1.0	_	LSB	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V	
Analog input voltage		V _{AIN}	0	_	VREFH0	V	_	

- Note 1. This value does not include the quantization error ($\pm 1/2$ LSB).
- Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- Note 3. When pins AN021 to AN022 are selected as the target pins for conversion, the maximum values are as follows.

Overall error: Add ±3 LSB to the maximum value.

Zero-scale/full-scale error: Add $\pm 0.04\%FSR$ to the maximum value.

Note 4. When reference voltage (+) = VCC (ADVREF[1:0] = 00b) and reference voltage (-) = VSS (ADVREFM = 0b), the maximum values are as follows.

Overall error: Add ±10 LSB to the maximum value.

Zero-scale/full-scale error: Add ±0.25%FSR to the maximum value.

Integral linearity error: Add ±4 LSB to the maximum value.

Note 5. When VREFH0 < VCC, the maximum values are as follows.

Overall error/zero-scale error/full-scale error: Add (±0.75 LSB × (VCC voltage (V) - VREFH0 voltage (V))) to the maximum value. Integral linearity error: Add (±0.2 LSB × (VCC voltage (V) - VREFH0 voltage (V))) to the maximum value.

Note 6. When the internal reference voltage or the temperature sensor output voltage is selected as the target for conversion, the sampling time must be at least 5 µs. Accordingly, use standard mode 2 with the longer sampling time.

Table 2.42 A/D conversion characteristics in Low-voltage modes 1 and 2 (1) (1 of 2)

Conditions: $1.6 \text{ V} \le \text{VREFH0} \le \text{VCC} \le 5.5 \text{ V}$, VSS = 0 V, $\text{Ta} = -40 \text{ to } +125 ^{\circ}\text{C}$

Reference voltage range applied to the VREFH0 (ADVREFP[1:0] = 01b) and VREFL0 (ADVREFM = 1b).

Target pins: AN000 to AN012, AN021 to AN022, internal reference voltage*7, and temperature sensor output voltage*7

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Resolution		RES	8	_	12	bit	_
Conversion clock		f _{AD}	1	_	24	MHz	_
Overall error*1 *3 *4 *5	12-bit	AINL	_	_	±9	LSB	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V
	resolution		_	_	±9	LSB	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±11.5	LSB	1.8 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±12.0	LSB	1.6 V ≤ VREFH0 = VCC ≤ 5.5 V

Table 2.42 A/D conversion characteristics in Low-voltage modes 1 and 2 (1) (2 of 2)

Conditions: 1.6 V \leq VREFH0 \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Reference voltage range applied to the VREFH0 (ADVREFP[1:0] = 01b) and VREFL0 (ADVREFM = 1b).

Target pins: AN000 to AN012, AN021 to AN022, internal reference voltage*7, and temperature sensor output voltage*7

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Conversion time*6	12-bit	t _{CONV}	3.3	_	_	μs	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V
	resolution		5.0	_	_	μs	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V
			10.0	_	_	μs	1.8 V ≤ VREFH0 = VCC ≤ 5.5 V
			20.0	_	_	μs	1.6 V ≤ VREFH0 = VCC ≤ 5.5 V
Zero-scale error*1 *2 *3 *4 *5	12-bit	E _{ZS}	_	_	±0.21	%FSR	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V
	resolution		_	_	±0.21	%FSR	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±0.27	%FSR	1.8 V ≤ VREFH0 = VCC ≤ 5.5 V
		_	_	±0.28	%FSR	1.6 V ≤ VREFH0 = VCC ≤ 5.5 V	
Full-scale error*1 *2 *3 *4 *5	12-bit	E _{FS}	_	_	±0.21	%FSR	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V
	resolution		_	_	±0.21	%FSR	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±0.27	%FSR	1.8 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±0.28	%FSR	1.6 V ≤ VREFH0 = VCC ≤ 5.5 V
Integral linearity error*1 *4 *5	12-bit		_	_	±4.0	LSB	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V
	resolution		_	_	±4.0	LSB	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±4.5	LSB	1.8 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	_	±4.5	LSB	1.6 V ≤ VREFH0 = VCC ≤ 5.5 V
Differential linearity error*1	12-bit	DLE	_	±1.5	_	LSB	2.7 V ≤ VREFH0 = VCC ≤ 5.5 V
	resolution		_	±1.5	_	LSB	2.4 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	±2.0	_	LSB	1.8 V ≤ VREFH0 = VCC ≤ 5.5 V
			_	±2.0	_	LSB	1.6 V ≤ VREFH0 = VCC ≤ 5.5 V
Analog input voltage	•	V _{AIN}	0	_	VREFH0	V	_

- Note 1. This value does not include the quantization error (±1/2 LSB).
- Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- Note 3. When pins AN021 to AN022 are selected as the target pins for conversion, the maximum values are as follows.

Overall error: Add ±3 LSB to the maximum value.

Zero-scale/full-scale error: Add ±0.04%FSR to the maximum value.

Note 4. When reference voltage (+) = VCC (ADVREF[1:0] = 00b) and reference voltage (-) = VSS (ADVREFM = 0b), the maximum values are as follows.

Overall error: Add ±10 LSB to the maximum value.

Zero-scale/full-scale error: Add ±0.25%FSR to the maximum value.

Integral linearity error: Add ±4 LSB to the maximum value.

- Note 5. When VREFH0 < VCC, the maximum values are as follows.
 - Overall error/zero-scale error/full-scale error: Add (±0.75 LSB × (VCC voltage (V) VREFH0 voltage (V))) to the maximum value. Integral linearity error: Add (±0.2 LSB × (VCC voltage (V) VREFH0 voltage (V))) to the maximum value.
- Note 6. When the internal reference voltage or the temperature sensor output voltage is selected as the target for conversion, the sampling time must be at least 5 µs. Accordingly, use standard mode 2 with the longer sampling time, and use the conversion clock (f_{AD}) of no more than 16 MHz.
- Note 7. If the internal reference voltage or temperature sensor output voltage is to be A/D converted, VCC must be at least 1.8 V.

Table 2.43 A/D conversion characteristics in Low-voltage modes 1 and 2 (2) (1 of 2)

Conditions: $1.8 \text{ V} \leq \text{VCC} \leq 5.5 \text{ V}$, VSS = 0 V, $\text{Ta} = -40 \text{ to } +125 ^{\circ}\text{C}$

Reference voltage range applied to the internal reference voltage (ADVREFP[1:0] = 10b) and VREFL0 (ADVREFM = 1b).

Parameter	Cumbal	Min	Tim	Max	Unit	Test conditions
Parameter	Symbol	IVIIII	Тур	IVIAX	Unit	rest conditions
Resolution	RES	8			bit	_
Conversion clock	f _{AD}	1	_	2	MHz	1.8 V ≤ VCC ≤ 5.5 V
Zero-scale error*1 *2 *4	E _{ZS}	_	_	±0.6	%FSR	1.8 V ≤ VCC ≤ 5.5 V
Integral linearity error*1 *4	ILE	_	_	±2.0	LSB	1.8 V ≤ VCC ≤ 5.5 V

Table 2.43 A/D conversion characteristics in Low-voltage modes 1 and 2 (2) (2 of 2)

Conditions: 1.8 V \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Reference voltage range applied to the internal reference voltage (ADVREFP[1:0] = 10b) and VREFL0 (ADVREFM = 1b).

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Differential linearity error*1	DLE	_	±1.0	_	LSB	1.8 V ≤ VCC ≤ 5.5 V
Analog input voltage	V _{AIN}	0	_	VBGR*3	V	_

- Note 1. This value does not include the quantization error (±1/2 LSB).
- Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- Note 3. Refer to Table 2.46.
- Note 4. When reference voltage (-) is selected as VSS, the maximum values are as follows. Zero-scale error: Add ±0.35%FSR to the maximum value.

Integral linearity error: Add ±0.5 LSB to the maximum value.

Table 2.44 Resistance and capacitance values of equivalent circuit (Reference data)

Parameter	Min	Тур	Max	Unit	Test conditions		
Analog input capacitance	Cin	Refer to I/O input capacitance ((Cin), see T	able 2.12.			
	Cs*2	High-precision channel*1	_	_	9	pF	_
		Normal-precision channel*1	_	_	10		_
Analog input resistance	Rs*2	High-precision channel*1	_	_	11	kΩ	VCC = 2.4 to 5.5 V
			_	_	55		VCC = 1.8 to 2.4 V
			_	_	110		VCC = 1.6 to 1.8 V
		Normal-precision channel*1	_	_	12		VCC = 2.4 to 5.5 V
			_	_	60		VCC = 1.8 to 2.4 V
			_	_	120		VCC = 1.6 to 1.8 V

Note 1. AN000 to AN010 are the High-precision channels. AN021 and AN022 are the Normal- precision channels.

Note 2. These values are based on simulation. They are not production tested.

Figure 2.32 shows the equivalent circuit for analog input.

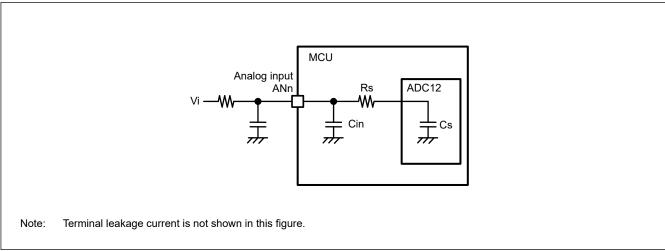


Figure 2.32 Equivalent circuit for analog input

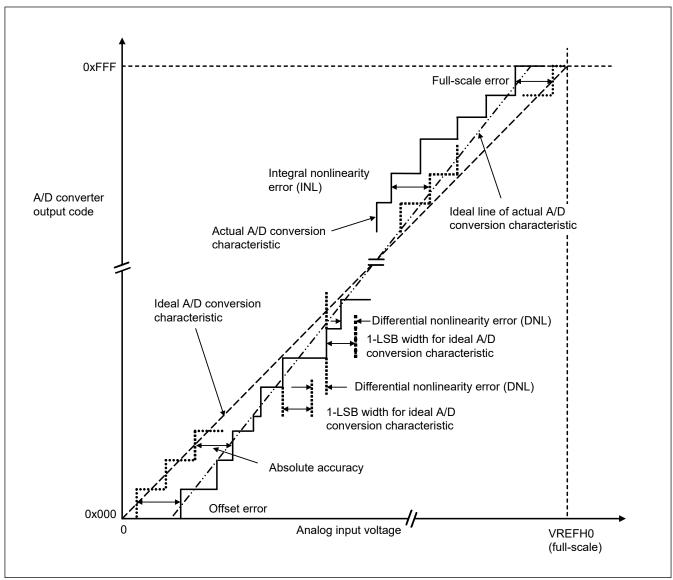


Figure 2.33 Illustration of 12-bit A/D converter characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as the analog input voltage. For example, if 12-bit resolution is used and the reference voltage VREFH0 = 3.072 V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If analog input voltage is 6 mV, an absolute accuracy of ± 5 LSB means that the actual A/D conversion result is in the range of 0x003 to 0x00D, though an output code of 0x008 can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

2.6.2 CTSU Characteristics

Table 2.45 CTSU characteristics

Conditions: VCC = 1.8 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
External capacitance connected to TSCAP pin	C _{tscap}	9	10	11	nF	_

2.6.3 Temperature Sensor/Internal Reference Voltage Characteristics

Table 2.46 Temperature sensor/internal reference voltage characteristics

Conditions: 1.8 V \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125 °C

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Temperature sensor output voltage	V _{TMPS25}	_	1.05	_	V	Ta: 25 °C
Internal reference voltage	V _{BGR}	1.40	1.48	1.56	V	_
Temperature coefficient	F _{VTMPS}	_	-3.3	_	mV/°C	_
Operation stabilization wait time	t _{AMP}	5	_	_	μs	_

2.6.4 POR Characteristics

Table 2.47 POR characteristics

Conditions: VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions
Detection voltage	VPOR VPDR	1.43	1.50	1.57	V	_
Minimum pulse width*1	TPW	300	_	_	μs	_

Note 1. This width is the minimum time required for a POR reset when VCC falls below VPDR. This width is also the minimum time required for a POR reset from when VCC falls below 0.7 V to when VCC exceeds VPOR in the Software standby mode or while the main system clock is stopped through setting HOCOCR.HCSTOP bit and MOSCCR.MOSTP bit.

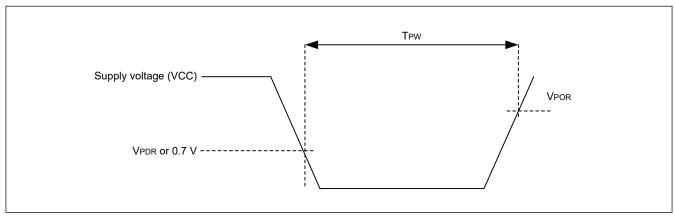


Figure 2.34 Minimum VCC pulse width

2.6.5 LVD Characteristics

Table 2.48 LVD0 characteristics

Conditions: VPDR \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min	Тур	Max	Unit	Test Conditions
Detection voltage	Supply voltage level	V _{det0_0}	3.84	3.96	4.08	V	The power supply voltage is rising.
			3.76	3.88	4.00	V	The power supply voltage is falling.
		V _{det0_1}	2.88	2.97	3.06	V	The power supply voltage is rising.
			2.82	2.91	3.00	V	The power supply voltage is falling.
		V _{det0_2}	2.59	2.67	2.75	V	The power supply voltage is rising.
			2.54	2.62	2.70	V	The power supply voltage is falling.
		V _{det0_3}	2.31	2.38	2.45	V	The power supply voltage is rising.
			2.26	2.33	2.40	V	The power supply voltage is falling.
		V _{det0_4}	1.84	1.90	1.95	V	The power supply voltage is rising.
			1.80	1.86	1.91	V	The power supply voltage is falling.
		V _{det0_5}	1.64	1.69	1.74	V	The power supply voltage is rising.
			1.60	1.65	1.70	V	The power supply voltage is falling.
Minimum pulse widtl	n	t _{LW0}	500	_	_	μs	_
Detection delay time		t _{det0}			500	μs	_

Table 2.49 LVD1 characteristics (1 of 2)

Conditions: VPDR \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min	Тур	Max	Unit	Test Conditions
Detection voltage	Supply voltage level	V _{det1_0}	4.08	4.16	4.24	V	The power supply voltage is rising.
			4.00	4.08	4.16	V	The power supply voltage is falling.
		V _{det1_1}	3.88	3.96	4.04	V	The power supply voltage is rising.
			3.80	3.88	3.96	V	The power supply voltage is falling.
		V _{det1_2}	3.68	3.75	3.82	V	The power supply voltage is rising.
			3.60	3.67	3.74	V	The power supply voltage is falling.
		V _{det1_3}	3.48	3.55	3.62	V	The power supply voltage is rising.
			3.40	3.47	3.54	V	The power supply voltage is falling.
		V _{det1_4}	3.28	3.35	3.42	V	The power supply voltage is rising.
			3.20	3.27	3.34	V	The power supply voltage is falling.
		V _{det1_5}	3.07	3.13	3.19	V	The power supply voltage is rising.
			3.00	3.06	3.12	V	The power supply voltage is falling.
		V _{det1_6}	2.91	2.97	3.03	V	The power supply voltage is rising.
			2.85	2.91	2.97	V	The power supply voltage is falling.
		V _{det1_7}	2.76	2.82	2.87	V	The power supply voltage is rising.
			2.70	2.76	2.81	V	The power supply voltage is falling.
		V _{det1_8}	2.61	2.66	2.71	V	The power supply voltage is rising.
			2.55	2.60	2.65	V	The power supply voltage is falling.
		V _{det1_9}	2.45	2.50	2.55	V	The power supply voltage is rising.
			2.40	2.45	2.50	V	The power supply voltage is falling.
		V _{det1_A}	2.35	2.40	2.45	V	The power supply voltage is rising.
			2.30	2.35	2.40	V	The power supply voltage is falling.

Table 2.49 LVD1 characteristics (2 of 2)

Conditions: VPDR \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	Min	Тур	Max	Unit	Test Conditions
Detection voltage	Supply voltage level	V _{det1_B}	2.25	2.30	2.34	V	The power supply voltage is rising.
			2.20	2.25	2.29	V	The power supply voltage is falling.
		V _{det1_C}	2.15	2.20	2.24	V	The power supply voltage is rising.
			2.10	2.15	2.19	V	The power supply voltage is falling.
		V _{det1_D}	2.05	2.09	2.13	V	The power supply voltage is rising.
			2.00	2.04	2.08	V	The power supply voltage is falling.
		V _{det1_E}	1.94	1.98	2.02	V	The power supply voltage is rising.
			1.90	1.94	1.98	V	The power supply voltage is falling.
		V _{det1_F}	1.84	1.88	1.91	V	The power supply voltage is rising.
			1.80	1.84	1.87	V	The power supply voltage is falling.
		V _{det1_10}	1.74	1.78	1.81	V	The power supply voltage is rising.
			1.70	1.74	1.77	V	The power supply voltage is falling.
		V _{det1_11}	1.64	1.67	1.70	V	The power supply voltage is rising.
			1.60	1.63	1.66	V	The power supply voltage is falling.
Minimum pulse wid	th	t _{LW1}	500	_	_	μs	_
Detection delay time	e	t _{det1}	_	-	500	μs	_
	age stabilization time LVD1 detection voltage)	t _{d(E-A)}	_	_	1500	μs	-

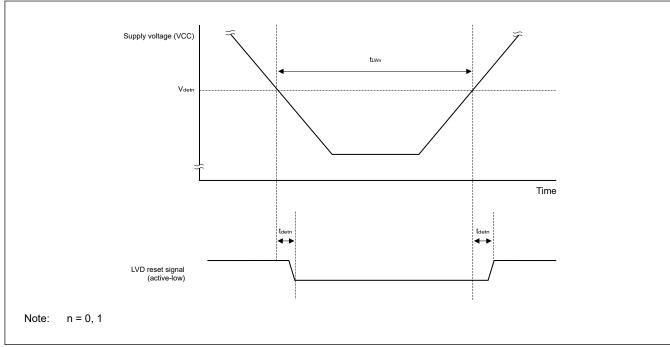


Figure 2.35 Voltage detection circuit timing

2.6.6 Power Supply Voltage Rising Slope Characteristics

Table 2.50 Power supply voltage rising slope characteristics

Conditions: VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Power supply voltage rising slope	S _{VCC}	_	_	54	V/ms	_

Note: Make sure to keep the internal reset state by the LVD0 circuit or an external reset until VCC reaches the operating voltage range shown in AC characteristics.

2.7 RAM Data Retention Characteristics

Table 2.51 RAM data retention characteristics

Conditions: VSS = 0 V, Ta = -40 to +125°C

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Data retention supply voltage	V _{CCDR}	1.43 ^{*1}	_	5.5	V	_

Note 1. This voltage depends on the POR detection voltage. When the voltage drops, the data in RAM are retained until a POR is applied, but are not retained following a POR.

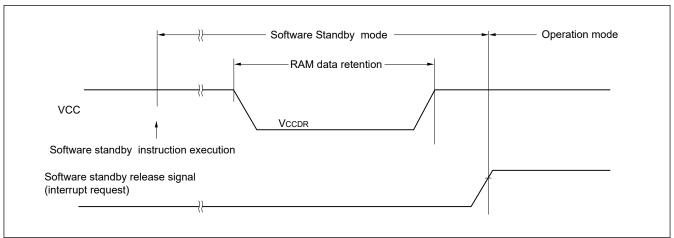


Figure 2.36 RAM data retention

2.8 Flash Memory Programming Characteristics

Table 2.52 Flash memory programming characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, VSS = 0 V, $\text{Ta} = -40 \text{ to } +125 ^{\circ}\text{C}$

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
CPU/peripheral hardware clock frequency	I _{CLK}	1	_	32	MHz	_
Number of code flash rewrites*1 *2 *3	Cerwr	10000	_	_	Times	Retained for 10 years Ta = 85°C
		1000	_	_		Retained for 20 years Ta = 85°C
Number of data flash rewrites*1 *2 *3		_	1000000	_		Retained for 1 year Ta = 25°C
		100000	_	_		Retained for 5 years Ta = 85°C
		10000	-	_		Retained for 20 years Ta = 85°C

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. The listed numbers of times apply when using the flash memory programmer and self-programming.
- Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Table 2.53 Code flash memory characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} \le 5.5 \text{ V}$, VSS = 0 V, $\text{Ta} = -40 \text{ to } +125 ^{\circ}\text{C}$

Parameter		Symbol	ICLK =	1 MHz		ICLK =	2 MHz, 3	3 MHz	4 MHz	≤ ICLK <	8 MHz	8 MHz ≤ ICLK < 32 MHz			ICLK = 32 MHz			Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Programming time	4 bytes	t _{P4}	_	74.7	656.5	_	51.0	464.6	_	41.7	384.8	_	37.1	346.2	_	34.2	321.9	μs
Erasure time	2 Kbytes	t _{E2K}	_	10.4	312.2	_	7.7	258.5	_	6.4	231.8	_	5.8	218.4	_	5.6	214.4	ms
Blank checking time	4 bytes	t _{BC4}	_	_	38.4	_	_	19.2	_	_	13.1	_	_	10.2	_	_	8.3	μs
ume	2 Kbytes	t _{BC2K}	_	_	2618.9	_	_	1309.5	_	_	658.3	_	_	332.8	_	_	234.1	μs
Time taken to fo the erasure	rcibly stop	t _{SED}	_	_	18.0	_	_	14.0	_	_	12.0	_	_	11.0	_	_	10.3	μs
Security setting	time	t _{AWSSAS}	_	18.0	525.5	_	14.3	468.7	_	12.5	440.7	_	11.6	426.7	_	11.3	422.3	ms
Time until progra starts following of of the Software instruction	cancellation	_	20	_	_	20	_	_	20	_	_	20	_	_	20	_	_	μs
Flash memory n transition wait tin		t _{DIS}	2	_	_	2	_	_	2	_	_	2	_	_	2	_	_	μs
Flash memory n transition wait tir		t _{MS}	15	_	_	15	_	_	15	_	_	15	_	_	15	_	_	μs

Note: The listed values do not include the time until the operations of the flash memory start following execution of an instruction by software.

Table 2.54 Data flash memory characteristics

Conditions: 1.8 V \leq VCC \leq 5.5 V, VSS = 0 V, Ta = -40 to +125°C

Parameter		Symbol	ICLK = 1 MHz		ICLK =	2 MHz, 3	3 MHz	4 MHz	≤ ICLK <	8 MHz	8 MHz 8 MHz ≤ ICLK < 32 MHz				ICLK = 32 MHz			
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Programming time	1 byte	t _{P4}	_	74.7	656.5	_	51.0	464.6	_	41.7	384.8	_	37.1	346.2	_	34.2	321.9	μs
Erasure time	256 bytes	t _{E2K}	_	7.8	259.2	_	6.4	232.0	_	5.8	218.5	_	5.5	211.8	_	5.4	209.7	ms
Blank checking time	1 byte	t _{BC4}	_	_	38.4	_	_	19.2	_	_	13.1	_	_	10.2	_	_	8.3	μs
ume	256 bytes	t _{BC2K}	_	_	1326.1	_	_	663.1	_	_	335.1	_	_	171.2	_	_	121.0	μs
Time taken to for the erasure	cibly stop	t _{SED}	_	_	18.0	_	_	14.0	_	_	12.0	_	_	11.0	_	_	10.3	μs
Time until progra starts following ca of the Software s instruction	ancellation	_	20	_	_	20	_	_	20	_	_	20	_	_	20	_	_	μs
Time until reading following setting l		t _{DSTOP}	0.25	_	_	0.25	_	_	0.25	_	_	0.25	_	_	0.25	_	_	μs
Flash memory metransition wait time		t _{DIS}	2	_	_	2	_	_	2	_	_	2	_	_	2	_	_	μs
Flash memory me transition wait tim		t _{MS}	15	_	_	15	_	_	15	_	_	15	_	_	15	_	_	μs

Note: The listed values do not include the time until the operations of the flash memory start following execution of an instruction by software.

2.9 Serial Wire Debug (SWD)

Table 2.55 SWD characteristics (1) (1 of 2)

Conditions: VCC = 2.4 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
SWCLK clock cycle time	t _{SWCKcyc}	80	_	_	ns	Figure 2.37
SWCLK clock high pulse width	tswckh	35	_	_	ns	
SWCLK clock low pulse width	t _{SECKL}	35	_	_	ns	
SWCLK clock rise time	tswckr	_	_	5	ns	
SWCLK clock fall time	tswckf	_	_	5	ns	

Table 2.55 SWD characteristics (1) (2 of 2)

Conditions: VCC = 2.4 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
SWDIO setup time	t _{SWDS}	16	_	_	ns	Figure 2.38
SWDIO hold time	tswdh	16	_	_	ns	
SWDIO data delay time	t _{SWDD}	2	_	70	ns	

Table 2.56 SWD characteristics (2)

Conditions: VCC = 1.6 to 2.4 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
SWCLK clock cycle time	tswckcyc	250	_	_	ns	Figure 2.37
SWCLK clock high pulse width	tswckh	120	_	_	ns	
SWCLK clock low pulse width	t _{SECKL}	120	_	_	ns	
SWCLK clock rise time	tswckr	_	_	5	ns	
SWCLK clock fall time	tswckf	_	_	5	ns	
SWDIO setup time	t _{SWDS}	50	_	_	ns	Figure 2.38
SWDIO hold time	t _{SWDH}	50	_	_	ns	
SWDIO data delay time	t _{SWDD}	2	_	170	ns	

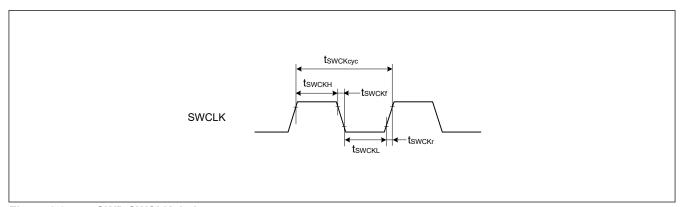


Figure 2.37 SWD SWCLK timing

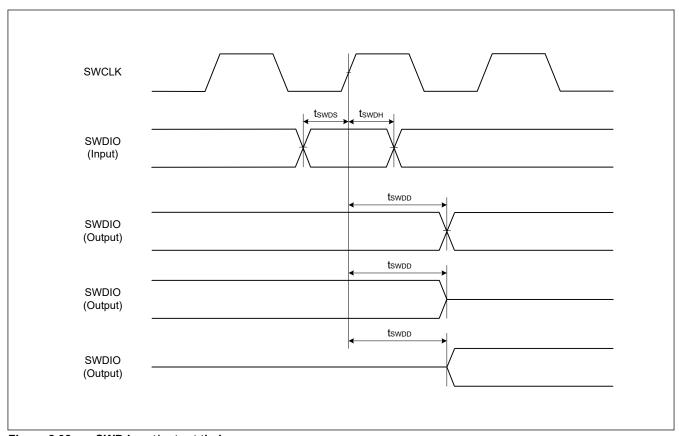


Figure 2.38 SWD input/output timing

RA0L1 Datasheet **Revision History**

Revision History

Revision 1.00 — January 31, 2024

Initial release

Revision 1.10 — July 31, 2025

Features:

• Updated Memory.

1. Overview:

- Updated Figure 1.1 Block diagram.
- Updated Table 1.15 Pin functions.
- Updated Table 1.16 Pin list.

2. Electrical Characteristics:

- Updated 32.5.1 Serial Array Unit (SAU).
 Updated 32.6.3 Temperature Sensor/Internal Reference Voltage Characteristics.
- Updated Table 32.15 Peripheral functions supply current.



General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

- 1. Precaution against Electrostatic Discharge (ESD)
 - A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.
- 2. Processing at power-on
 - The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.
- 3. Input of signal during power-off state
 - Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.
- 4. Handling of unused pins
 - Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible
- 5. Clock signals
 - After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.
- 6. Voltage application waveform at input pin
 - Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
- 7. Prohibition of access to reserved addresses
 - Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.
- 8. Differences between products
 - Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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